



16th International Toki Conference
Advanced Imaging and Plasma Diagnostics
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December 5, 16:40 – 17:10, Oral Session Plasma (Imaging Technology) I3-2



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Spectroscopy and Imaging by Laser Excited Terahertz Waves

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はんぎょう

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Outline

1. Introduction
2. THz radiation by femtosecond laser excitation
3. THz time domain spectroscopy (THz-TDS)
4. THz imaging
5. Summary

1. Introduction

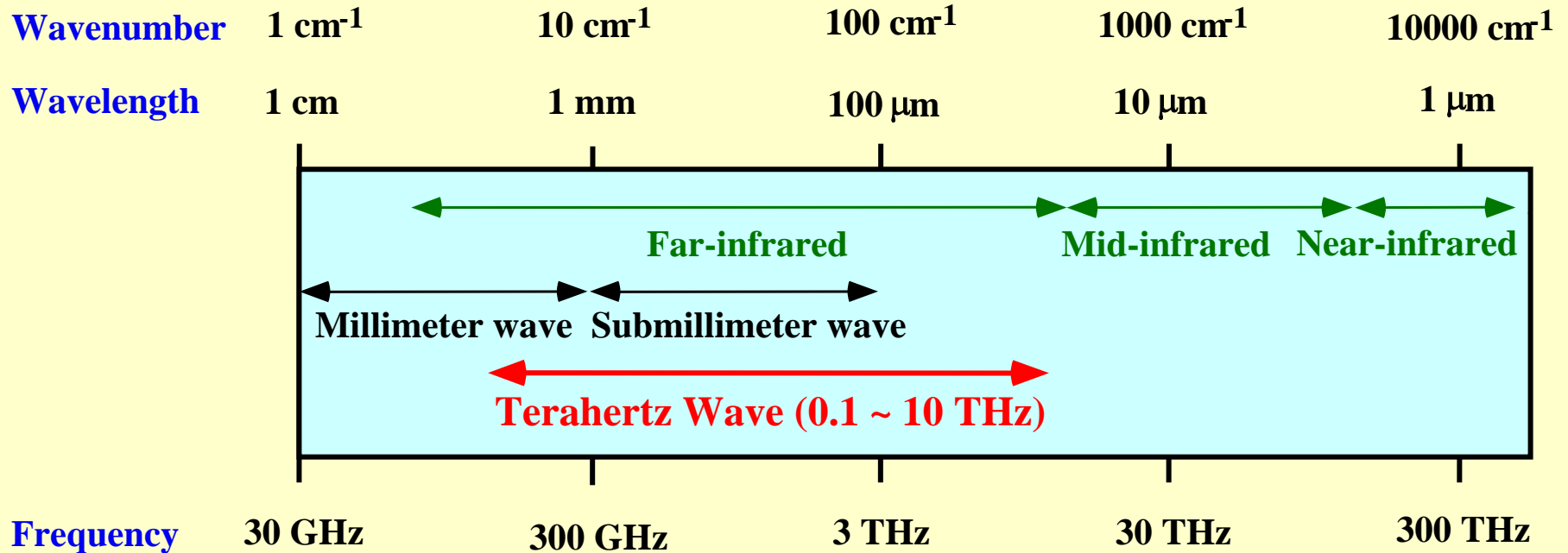
What is Terahertz (THz) Wave ?



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THz wave
Electromagnetic waves between microwave and visible light

$$1 \text{ THz} = 10^{12} \text{ Hz}$$



Unexploited region of electromagnetic waves until very recently

Various Excitations in THz Region



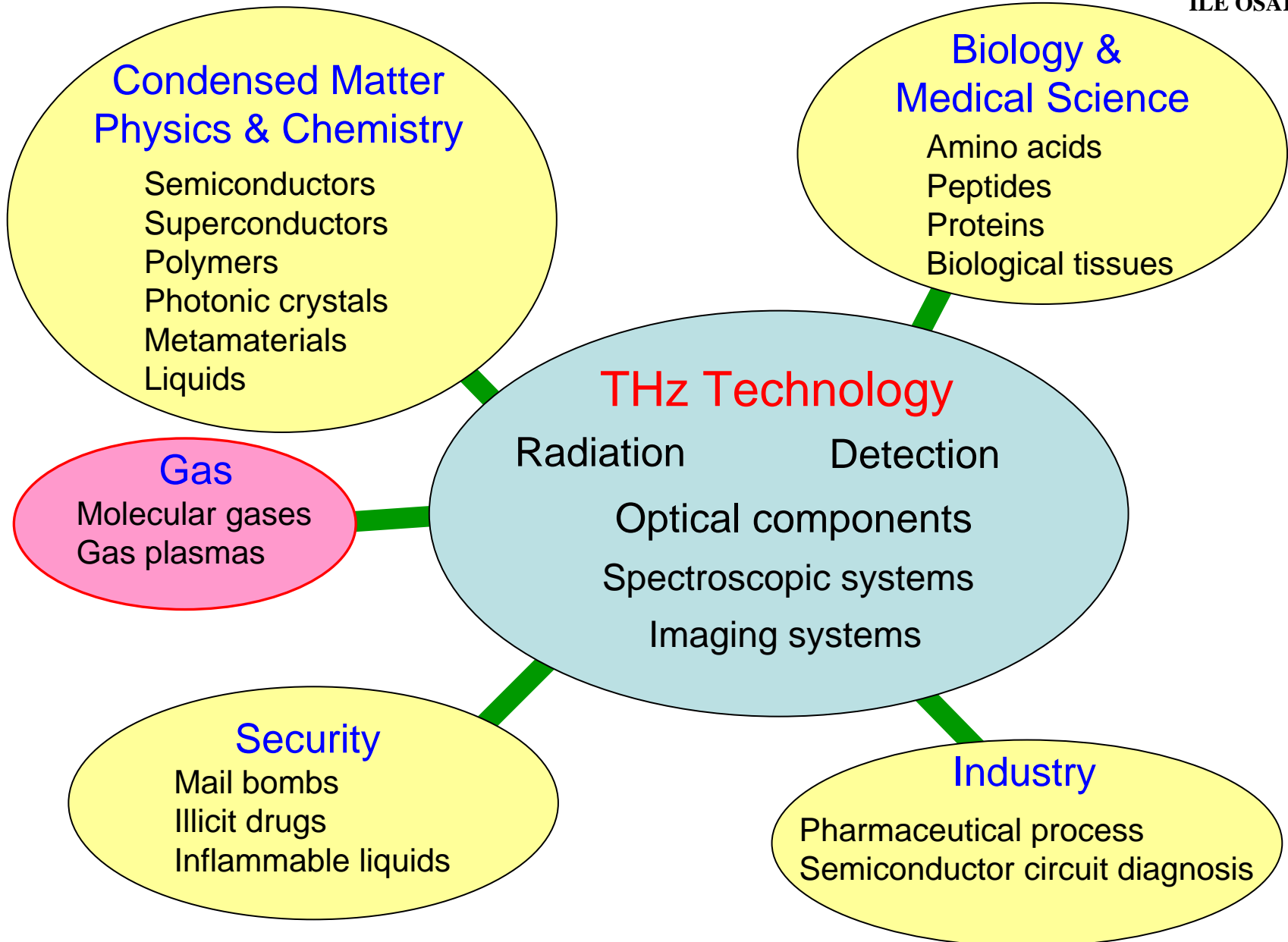
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Material	Excitation
Semiconductor	Free carrier, Phonon, Plasmon, LO phonon-plasmon coupled mode, Cyclotron resonance, Magnetoplasma
Ferroelectrics	Soft mode
Superconductor	Superconducting energy gap, Quasiparticle excitation, Intrinsic Josephson plasma, 2D-super carrier plasmon-polariton
Photonic crystal	Photonic band
Liquid	Relaxation mode
Gas	Rotational mode, Plasma
Biomolecule	Vibrational mode, Collective excitation related to biological function

Terahertz Technology and Its Applications



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2. THz radiation by femtosecond laser excitation



Excited by ultrashort laser pulses

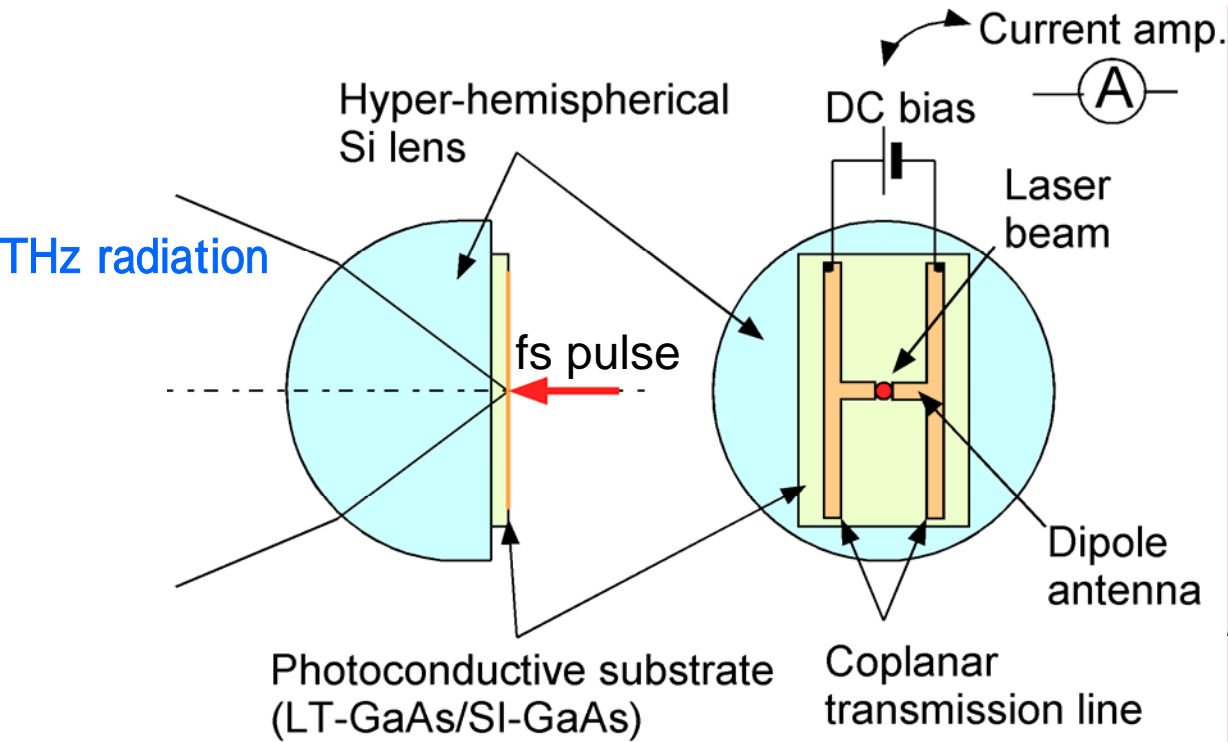
- ① Semiconductor photoconductive antennas (Auston switch)
2. Photoconduction at bulk semiconductor surfaces
3. Nonlinear optical effect in dielectrics and semiconductors
- ④ Ultrafast supercurrent modulation in high- T_c superconductors
5. Photo-ionization of gases under high electric fields
6. Various processes in ultraintense-laser-excited gas plasmas

THz Radiation from Photoconductive Antenna

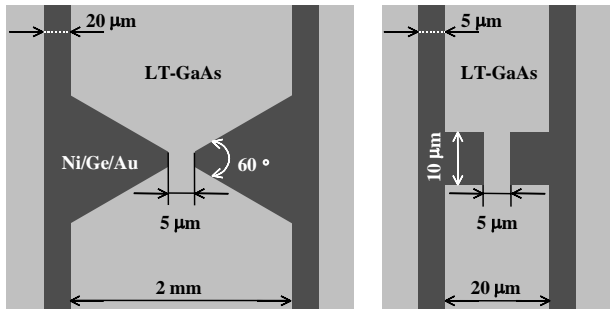
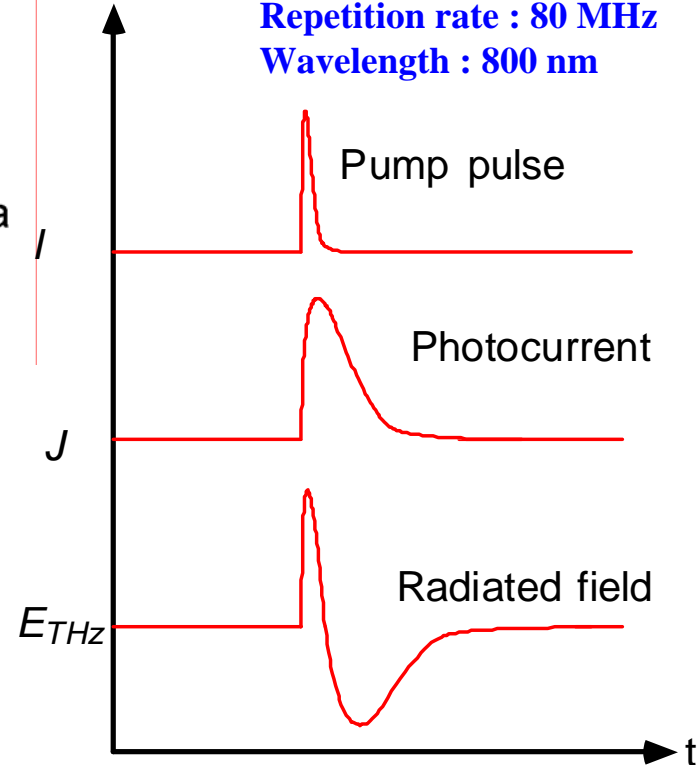


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Photoconductive antenna
 Photoconductive switch
 Auston switch



Time width : 50 fs
 Repetition rate : 80 MHz
 Wavelength : 800 nm



bowtie

dipole

$$E_{THz}(t) \propto \frac{dJ(t)}{dt}$$

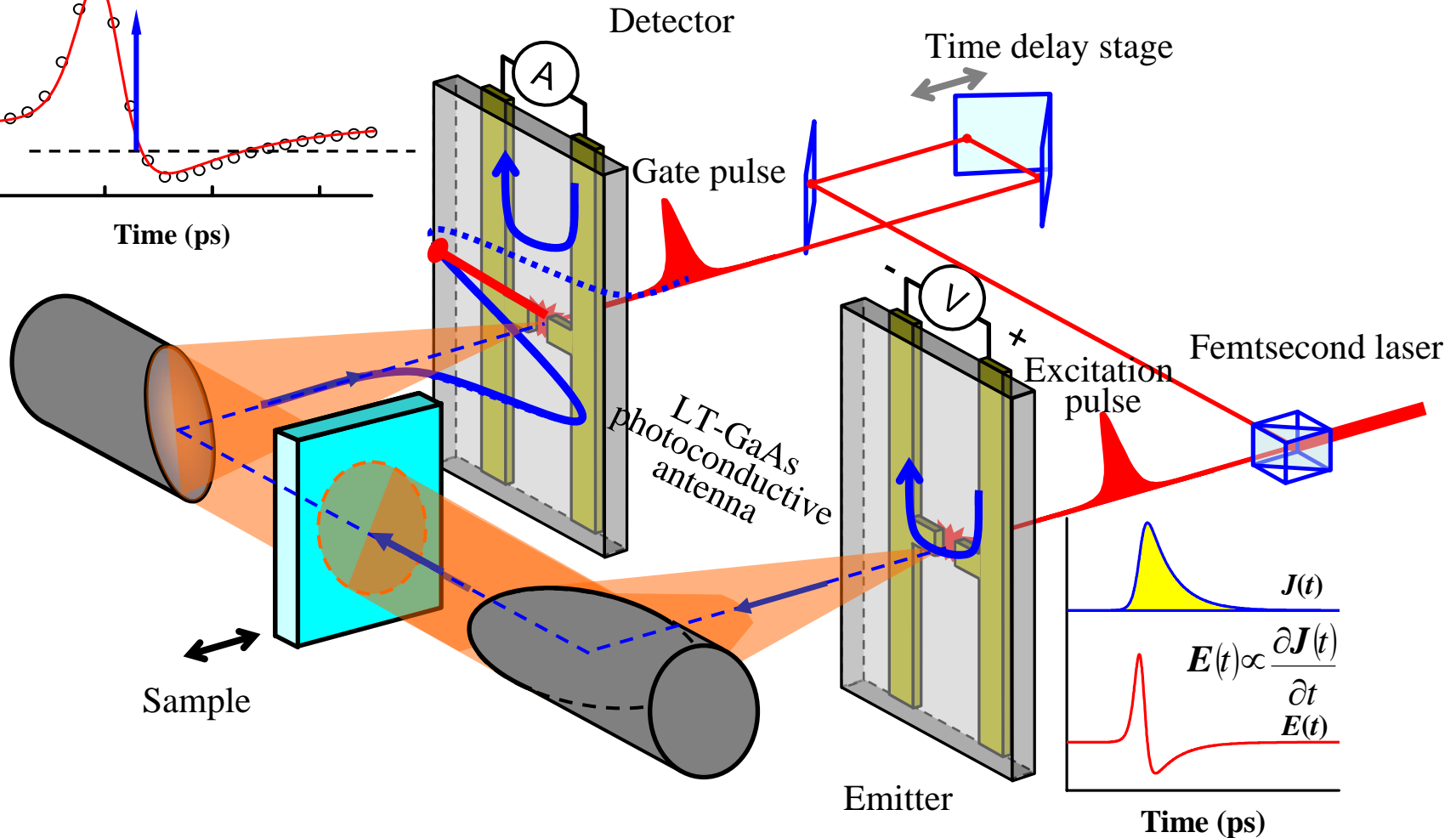
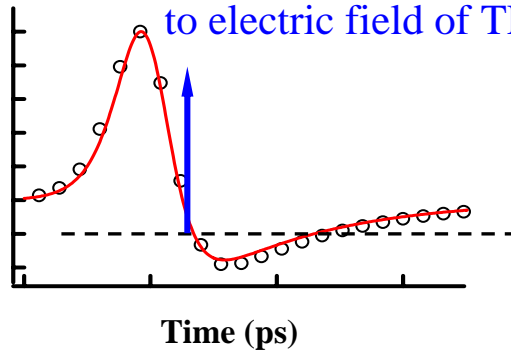
Emission and Detection of THz Waves



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Terahertz Time-Domain Spectroscopic System (THz-TDS)

Output current signal is proportional to electric field of THz wave.



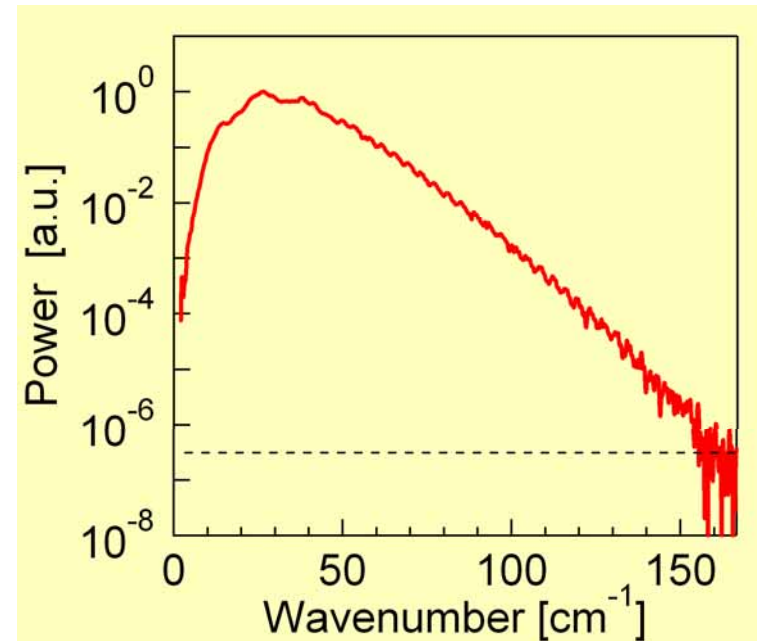
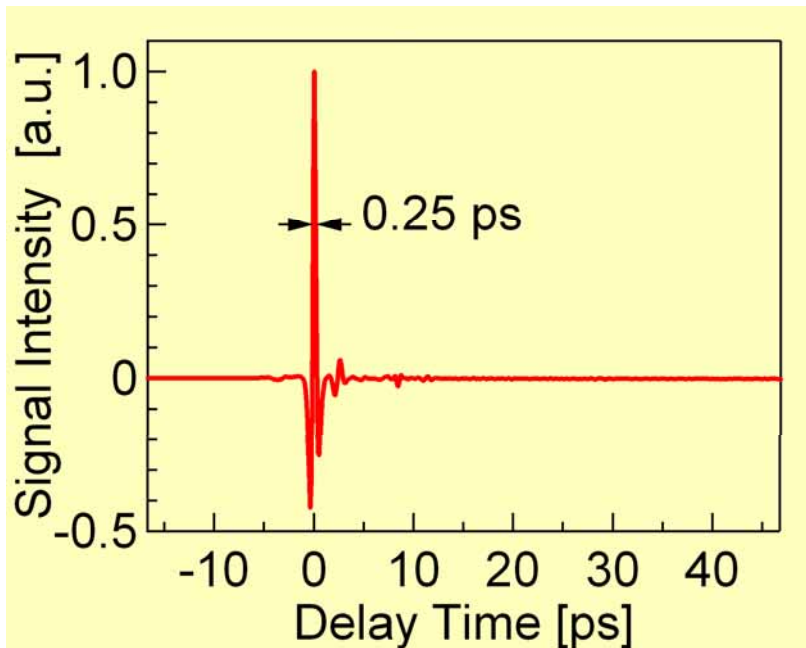
Developed as a spectroscopic system mainly by Grischkowsky's group (IBM)

Wave Form and Spectrum of THz Radiation



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Photoconductive antenna : 50 μ m dipole type
Laser pulse width : 80fs



Fourier Transformation

100 cm⁻¹ = 3 THz

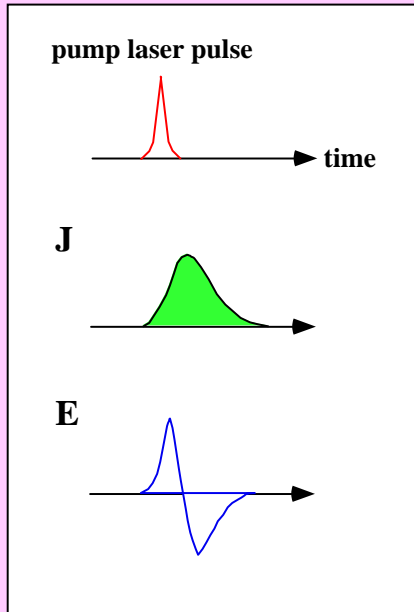
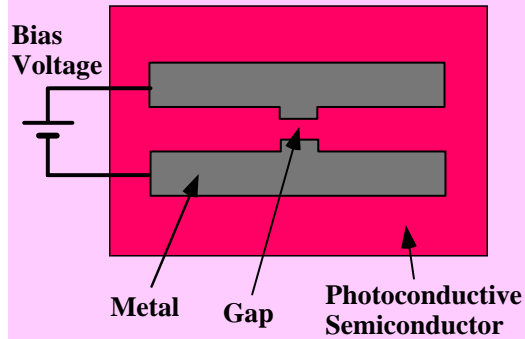
Broadband radiation from nearly 0 to 5 THz

Principle of THz Radiation from Superconductor

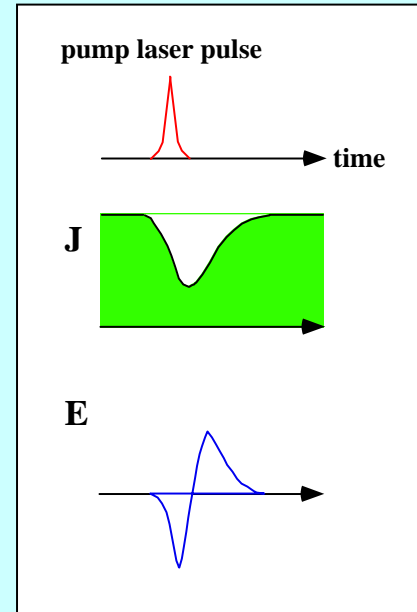
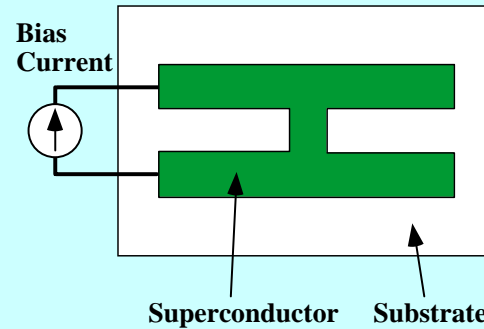


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Semiconductor



Superconductor



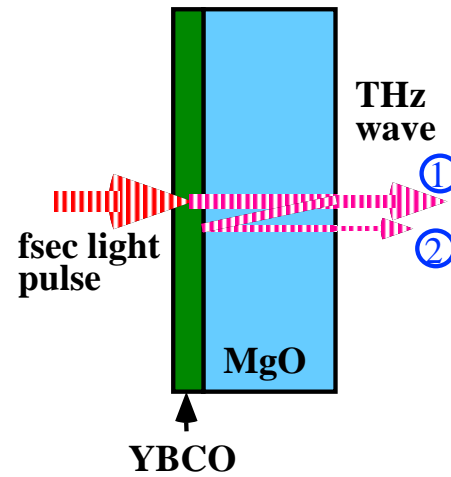
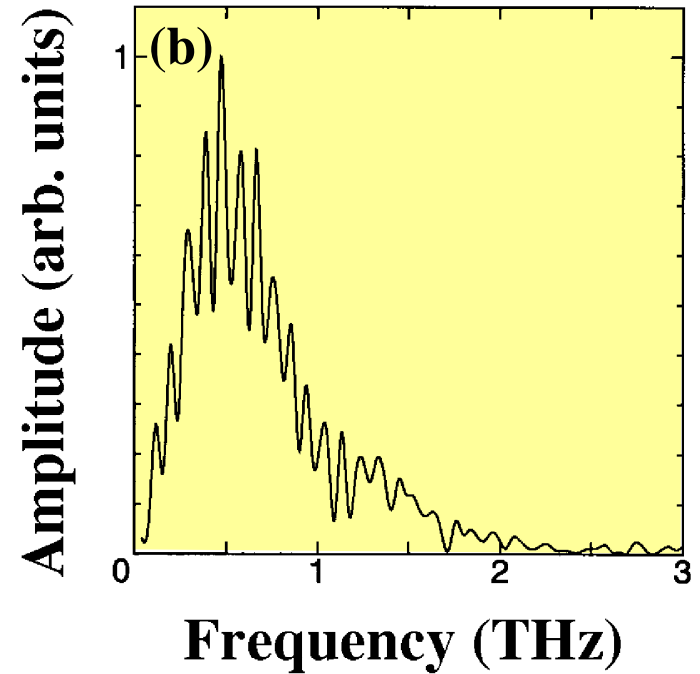
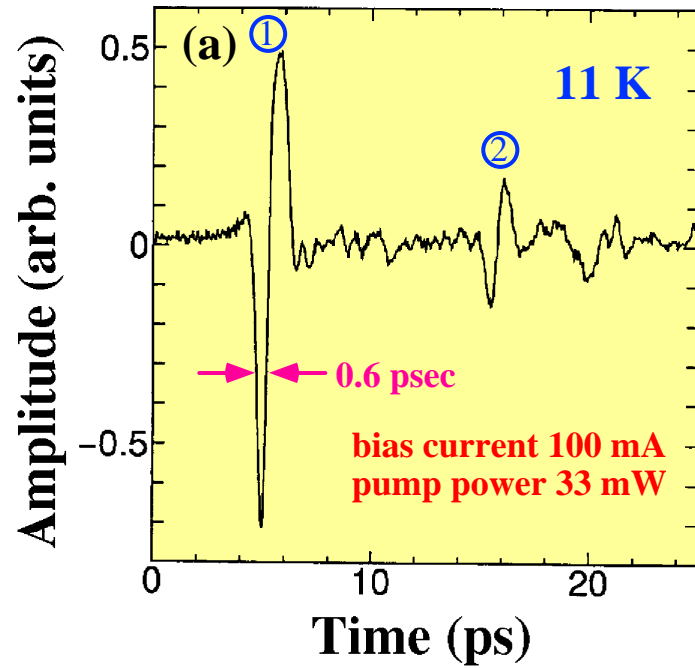
Ultrafast optical modulation of supercurrent

$$E \sim dJ / dt$$

THz Radiation from High- T_c Superconductor



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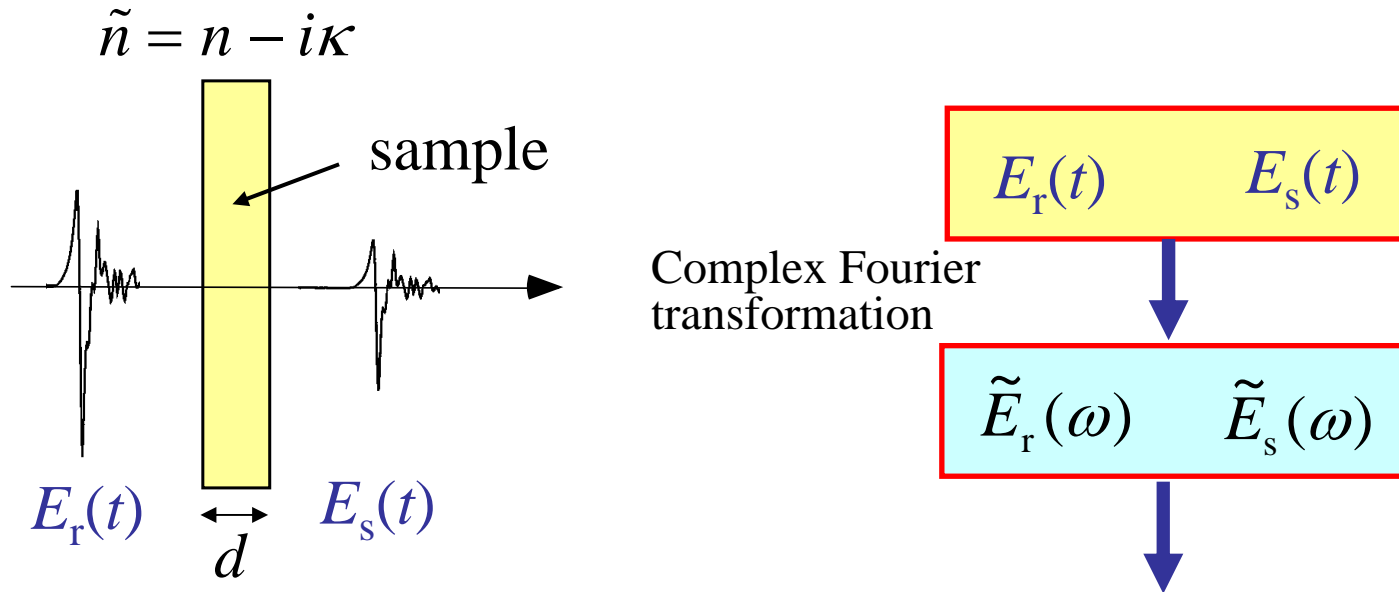


3. THz time domain spectroscopy (THz - TDS)

Principle of THz-TDS



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$$\sqrt{\text{Transmittance}} \exp(-i \text{Phase shift}) = \frac{\tilde{E}_s(\omega)}{\tilde{E}_r(\omega)}$$

$$= \tilde{t}_{\text{as}}(\omega) \tilde{t}_{\text{sa}}(\omega) \exp\left\{i \frac{(\tilde{n}(\omega) - 1)d\omega}{c}\right\} \sum_{l=0}^m \left\{ (r_{\text{sa}}(\omega))^2 \exp\left(i \frac{2\tilde{n}(\omega)d\omega}{c}\right) \right\}^l$$

Derivation of physical quantities

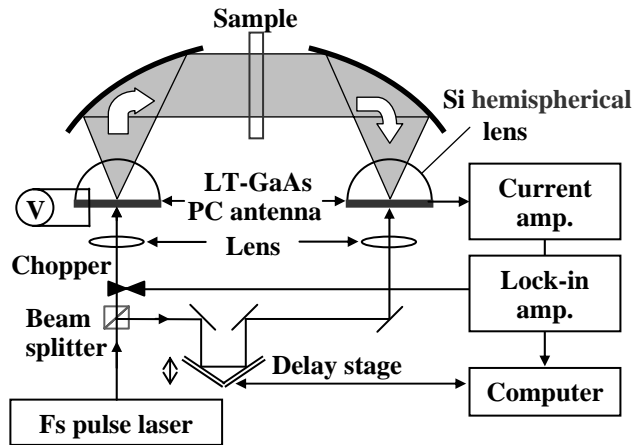
$$\tilde{n}(\omega)^2 = \tilde{\epsilon}(\omega) = \epsilon_{\text{Si}} - i\tilde{\sigma}(\omega) / \omega\epsilon_0$$

Various Types of THz-TDS System

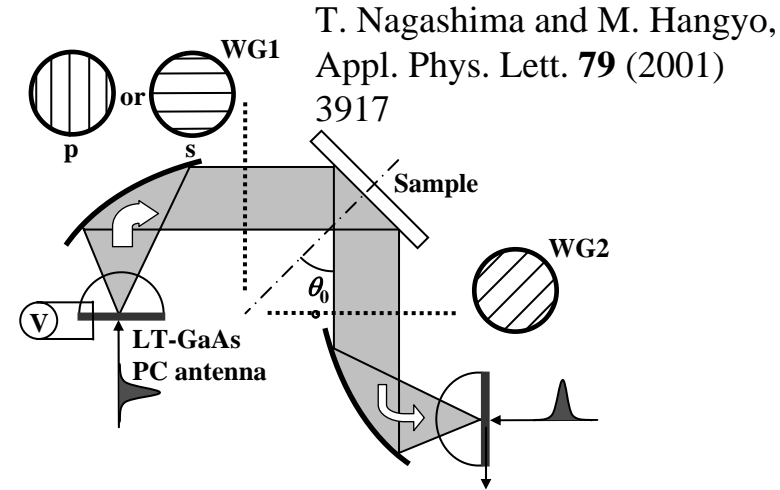


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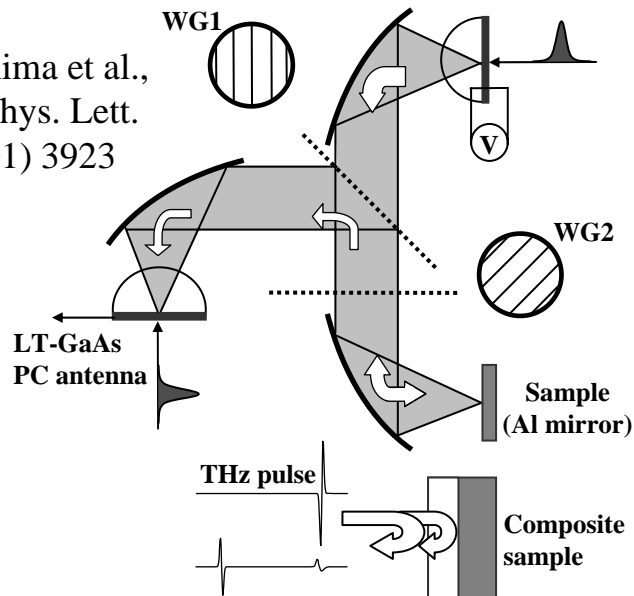
Transmission type



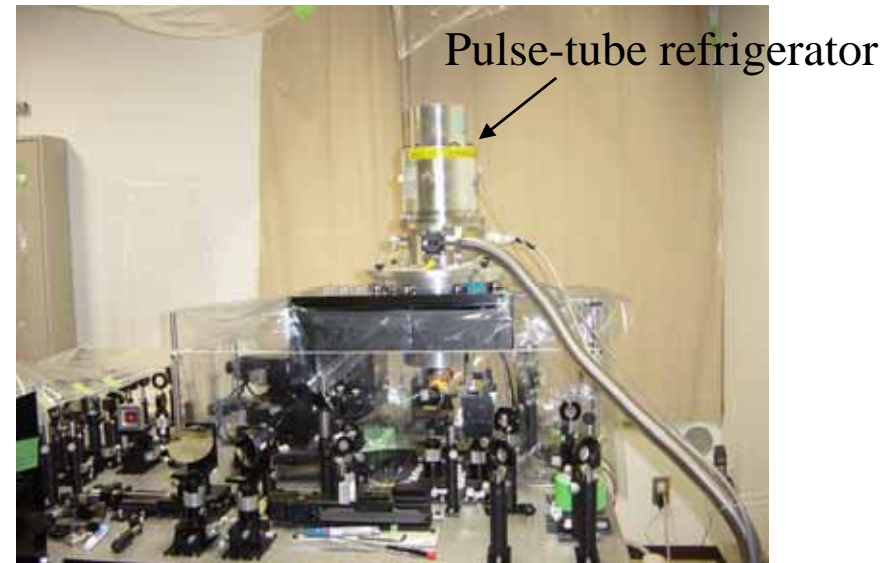
Ellipsometry type



Reflection type



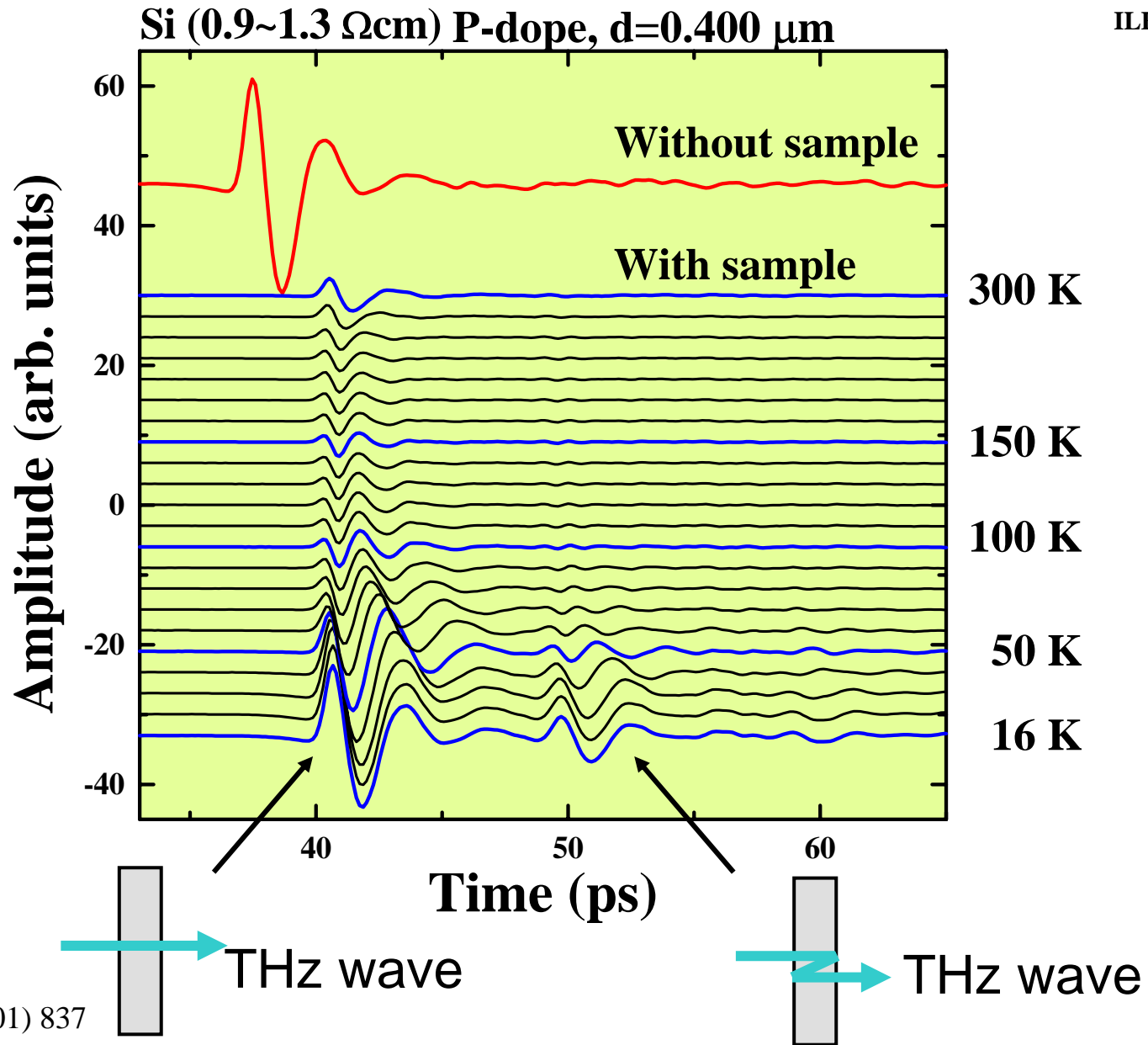
System for low-temperature measurements



THz - TDS of Doped Silicon



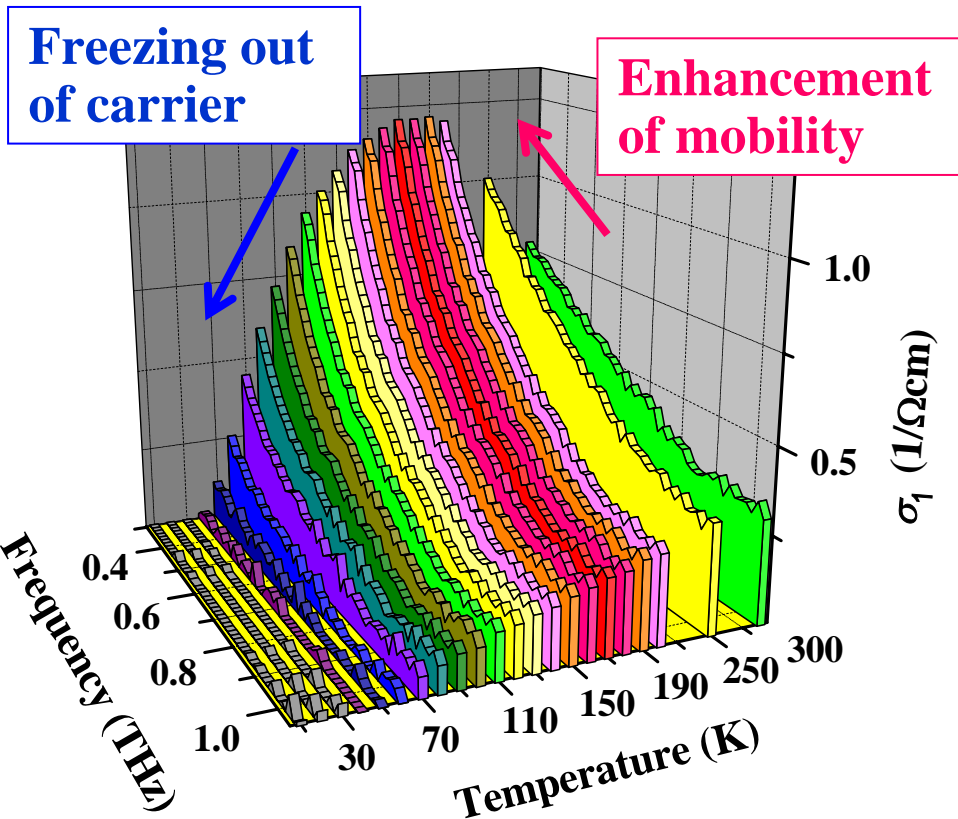
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Complex Conductivity Deduced from THz-TDS Data

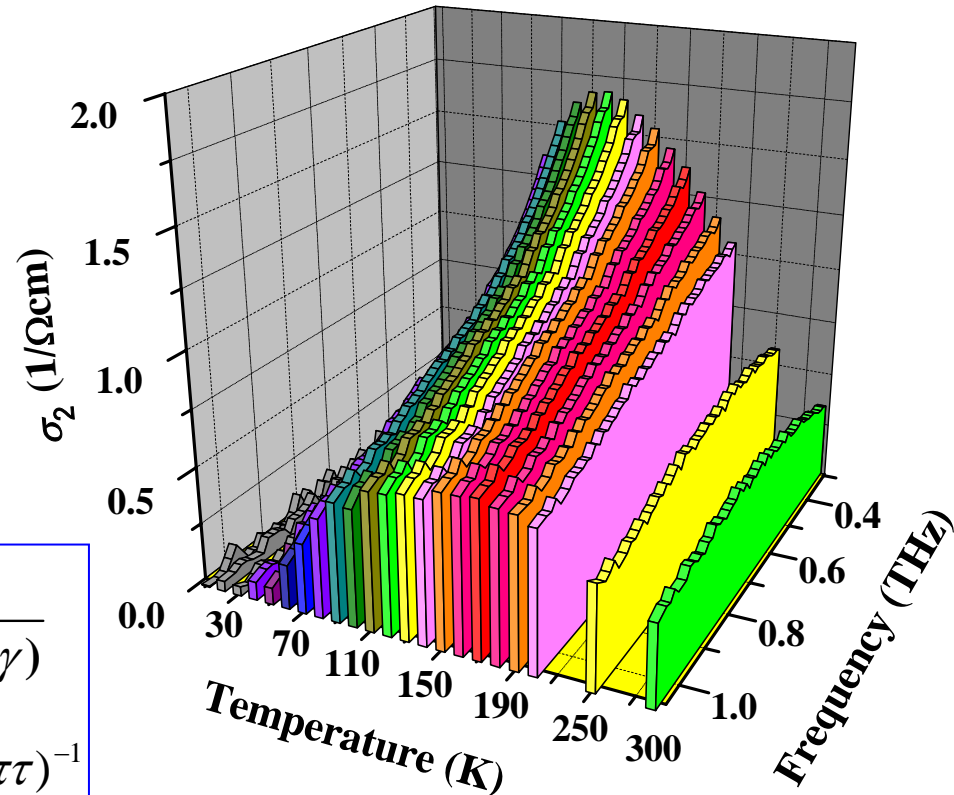


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$$\sigma_1(\omega) - i\sigma_2(\omega)$$

$$\tilde{n}^2 = \tilde{\epsilon}(\omega) = \epsilon_{Si} + i\tilde{\sigma}(\omega) / \omega\epsilon_0$$



Drude model

Dielectric function similar to that of gas plasma

$$\tilde{\epsilon}(\omega) = \epsilon_{Si} - \frac{\omega_p^2}{\omega(\omega + i\gamma)}$$

$$\omega_p^2 = \frac{n_c e^2}{\epsilon_0 m^*}, \quad \gamma = (2\pi\tau)^{-1}$$

High frequency conductivity σ_1 and σ_2 can be obtained without contact. By the Drude model fitting, the carrier density and mobility can be deduced.

Time Evolution of Gas Plasma



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Plasma characterization with terahertz time-domain measurements

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Jingling Shen

Department of Physics, Capital Normal University, Beijing, China

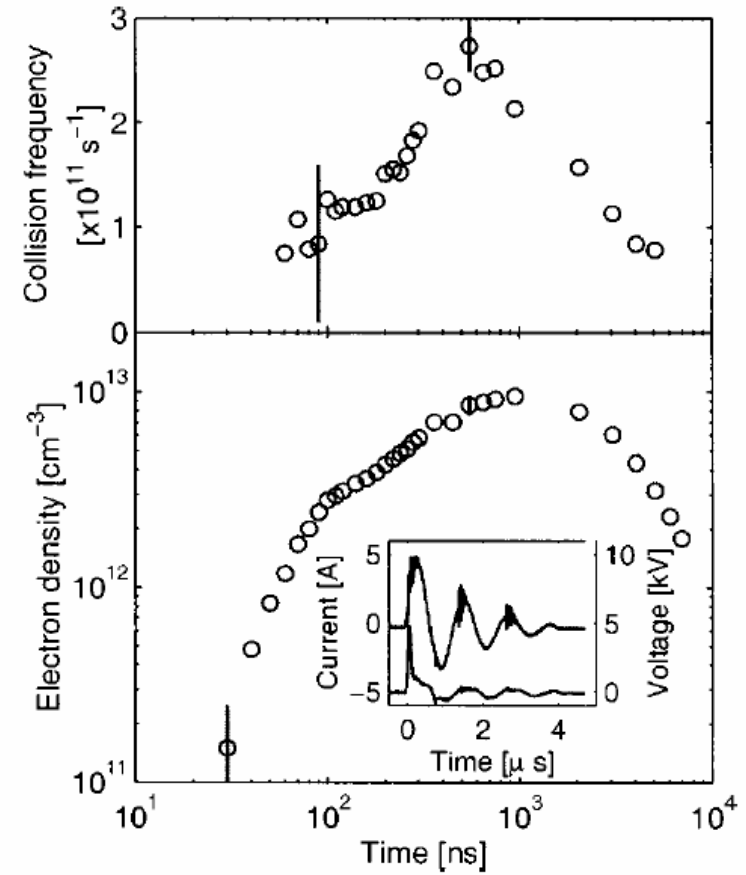
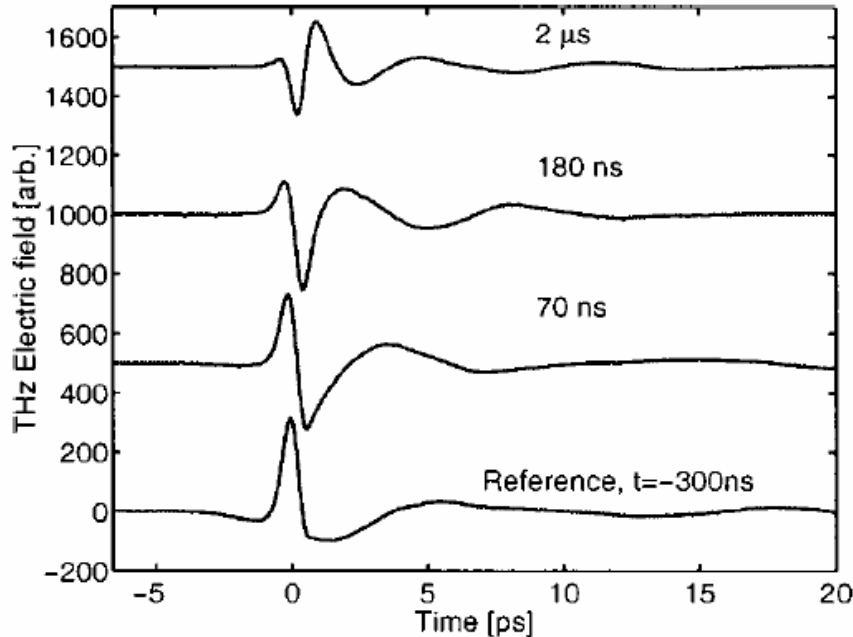
D. R. Jones, R. C. Issac, B. Ersfeld, D. Clark, and D. A. Jaroszynski

Department of Physics and Applied Physics, University of Strathclyde, Glasgow, G4 0NG, United Kingdom

$$\epsilon = \left(1 - \frac{\omega_p^2}{\omega^2 + \nu^2} \right) - i \left(\frac{\nu}{\omega} \frac{\omega_p^2}{\omega^2 + \nu^2} \right)$$
$$\omega_p = \sqrt{n_e e^2 / \epsilon_0 m_e}$$

He discharge plasma

15 cm long and 2 cm diameter plasma tube



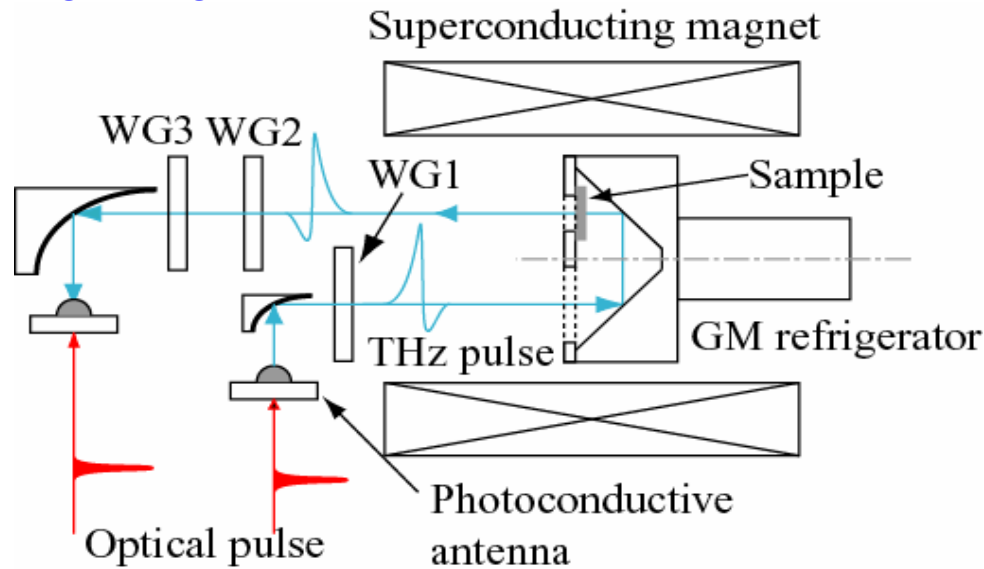
Probed by delayed THz pulses after discharge

THz Magneto-optical Measurement System

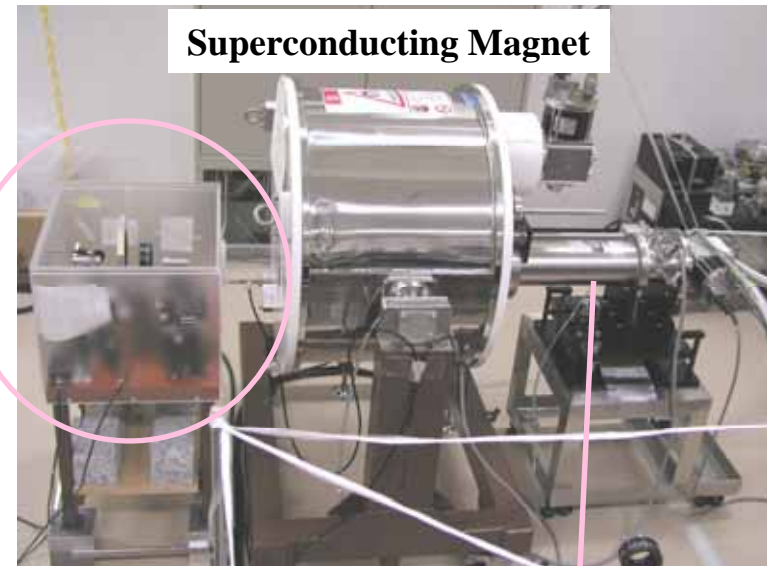


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High magnetic field (10 T) and low temperature (5 K)

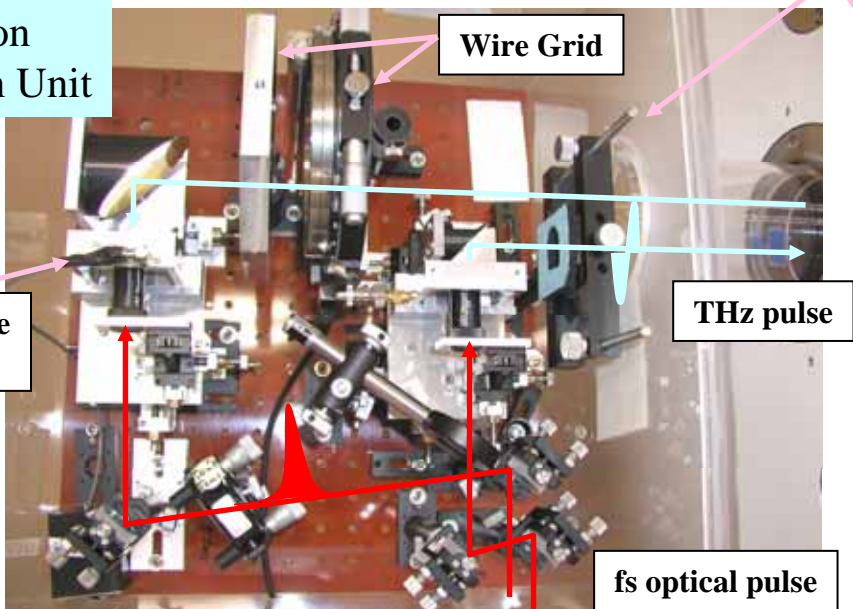


Rotation of the Wire grid polarizer
→ The polarization analysis



Superconducting Magnet

THz Emission & Detection Unit

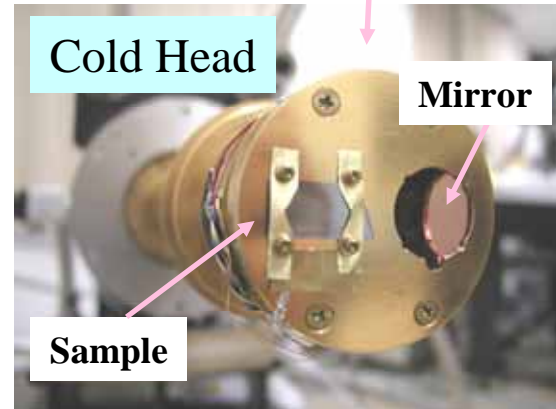


Photoconductive Antenna

Wire Grid

THz pulse

fs optical pulse



Cold Head

Mirror

Sample

THz Magneto-optical Effect of Si-doped GaAs



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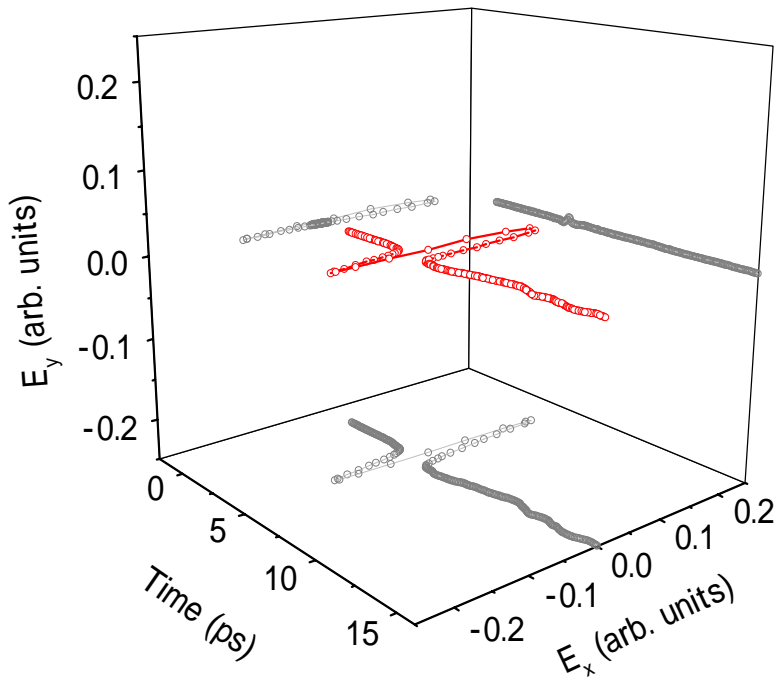
10 T, 5 K

Si-doped GaAs wafer (100), $d = 0.371$ mm

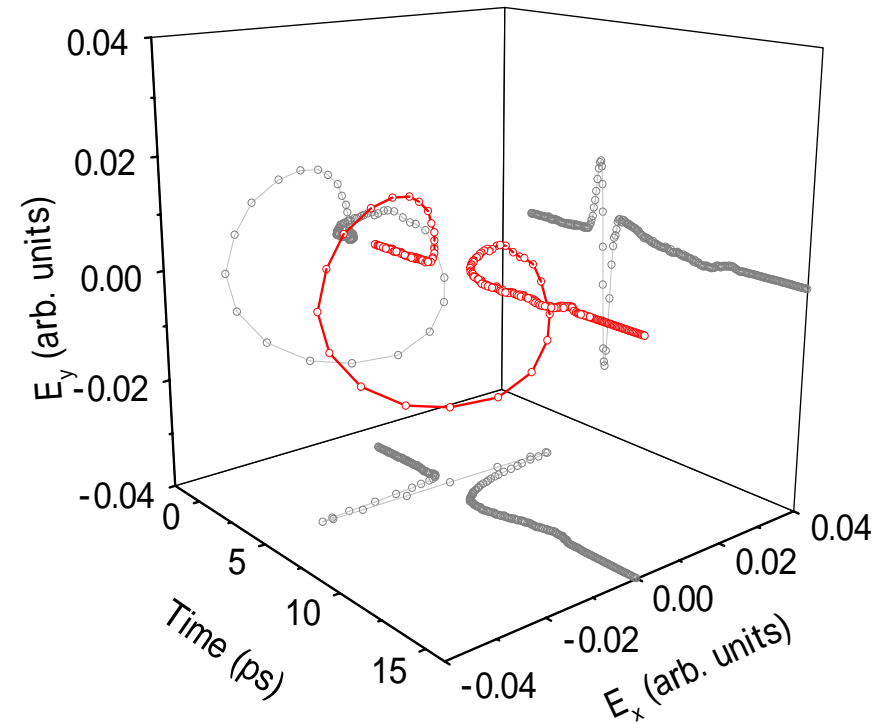
Carrier density 1.34×10^{16} cm⁻³, Mobility 3400 cm²/Vs at R.T.

Faraday effect

Incident THz pulse



Si-doped GaAs



THz waveform

F.T.



- Ellipticity
- Rotation angle

Temperature Dependence



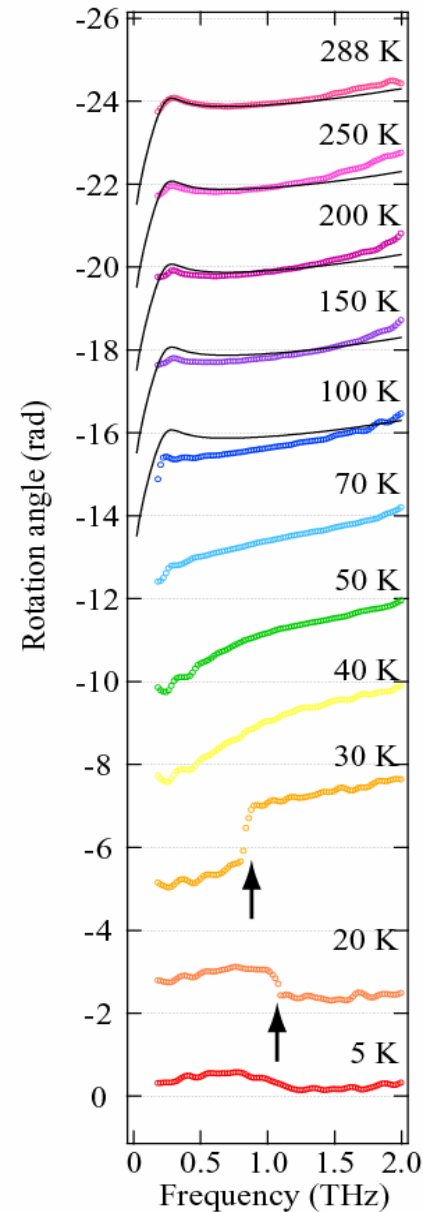
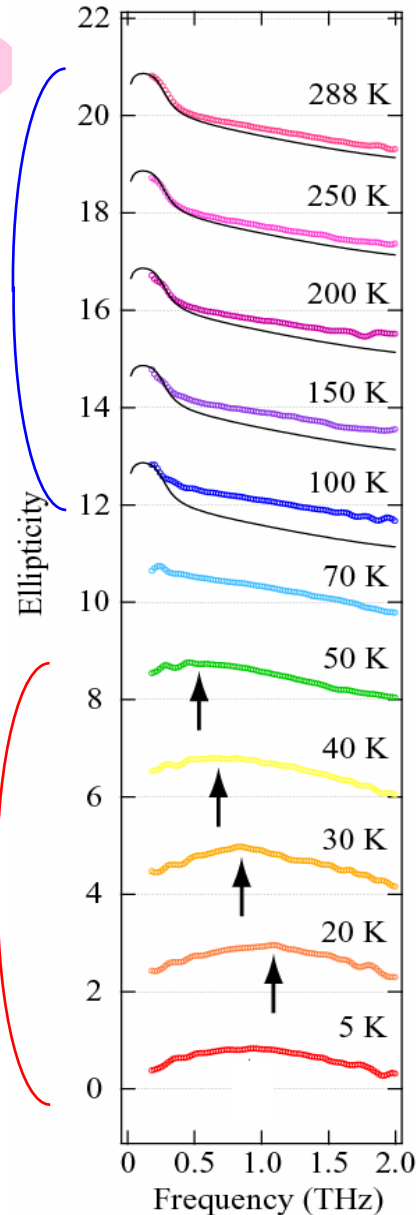
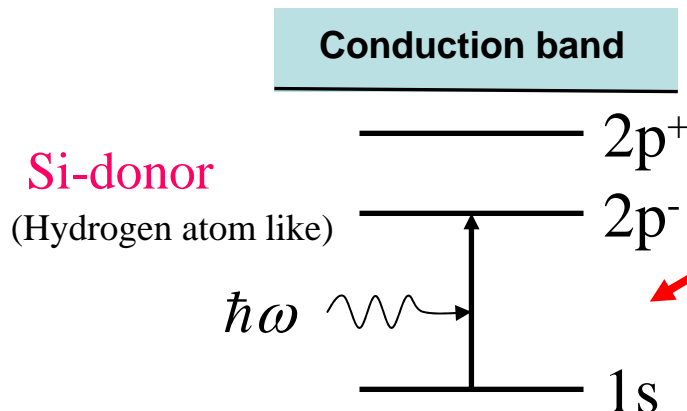
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$B = 10 \text{ T}$

High temperature

Black solid line : Drude fitting
($n_c = 1.34 \times 10^{16} \text{ cm}^{-3}$, $\tau = 0.13 \text{ ps}$)

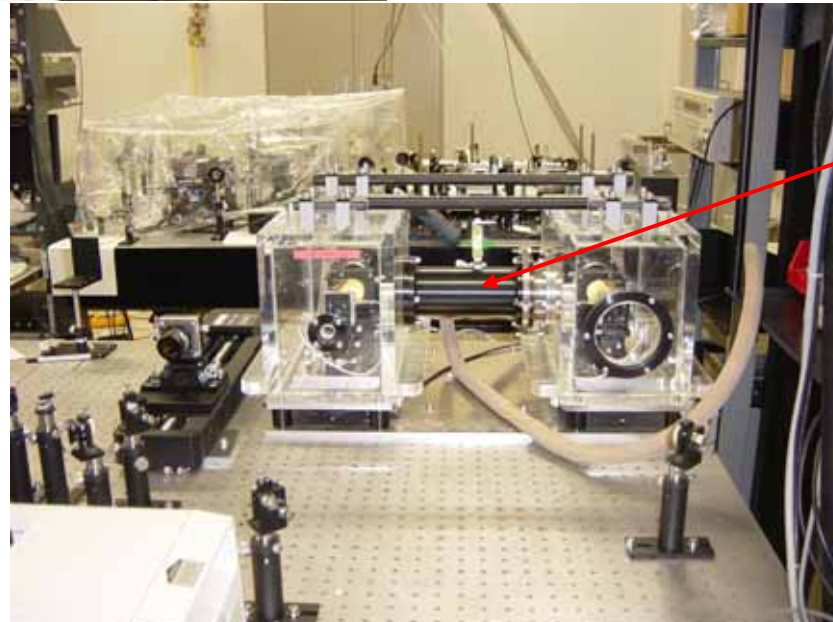
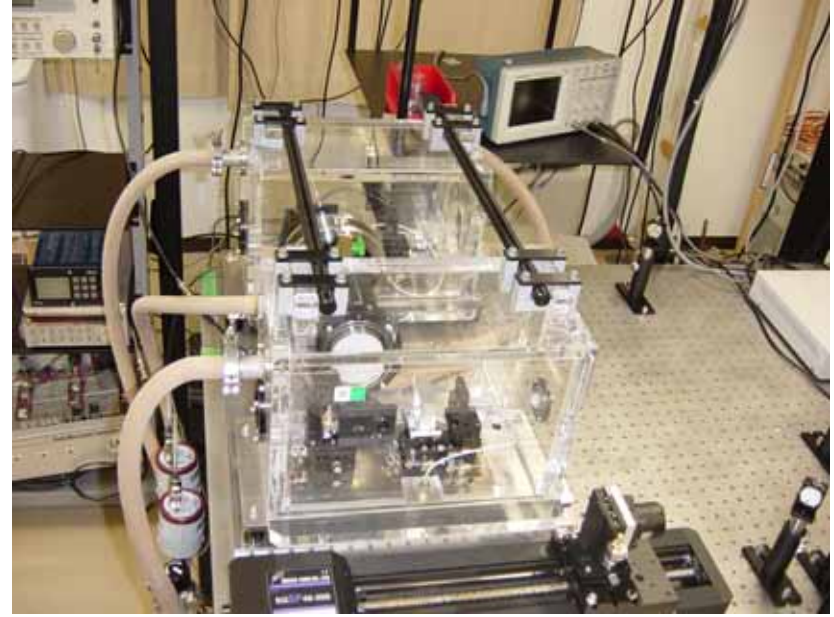
Low temperature



Measurement System for Gases



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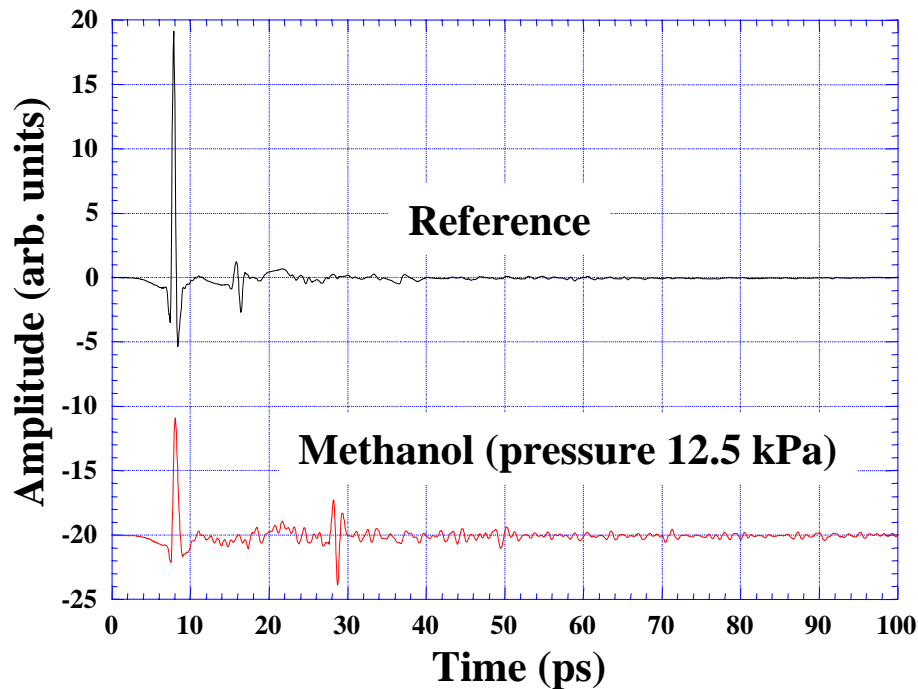
Gas cell

Transmission Spectrum of Methanol Gas



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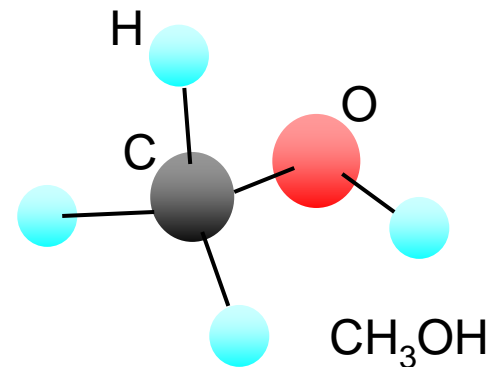
Time-domain wave form



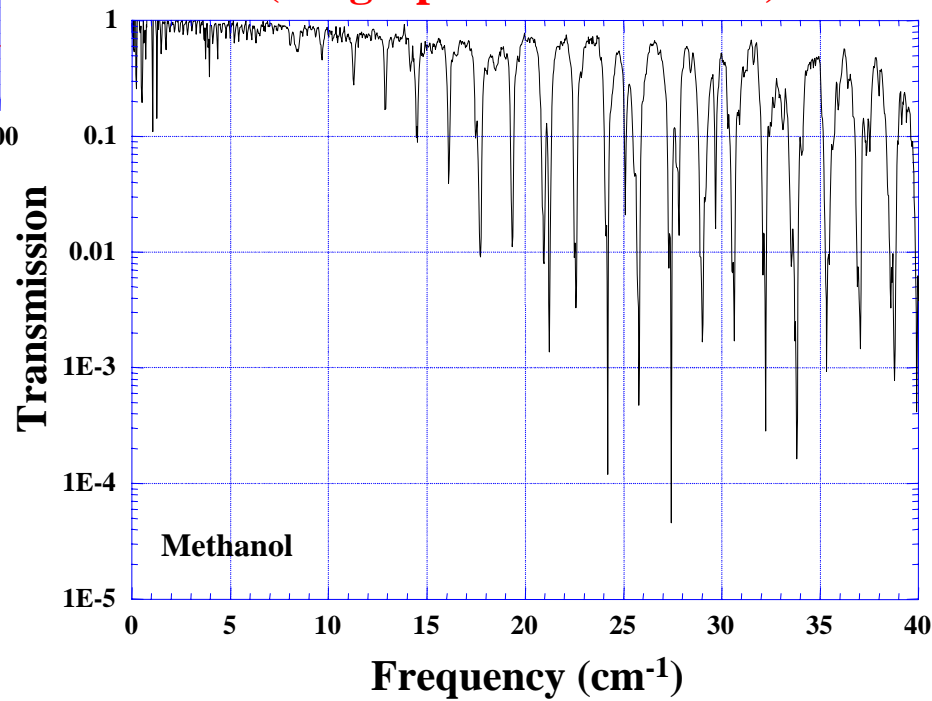
1 THz = 33 cm⁻¹

Identification of molecular gas species is possible.

Rotational transitions



Transmission spectrum
(Fingerprint of molecule)



4. THz imaging

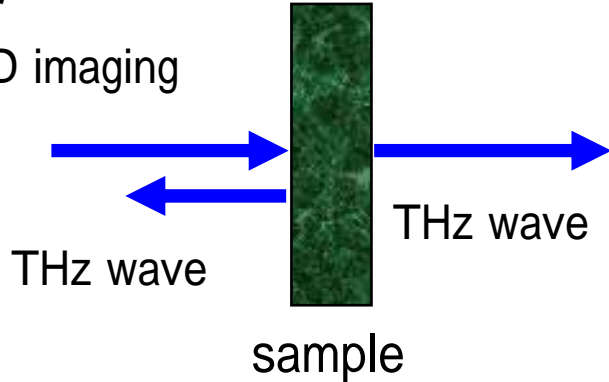
Two Types of Imaging Methods



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THz transmission and reflection imaging

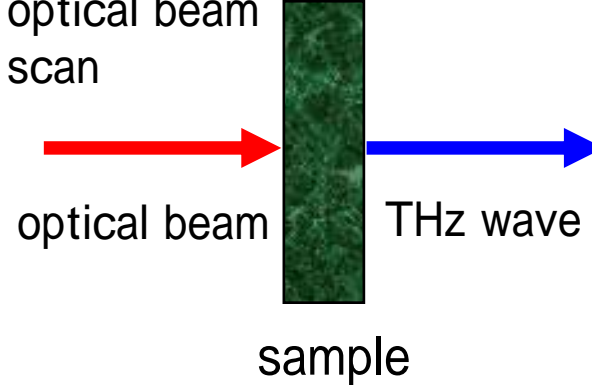
focused THz beam scan
or
2D imaging



- Conventional imaging method
- Applicable to most samples

THz emission imaging

focused
optical beam
scan



- Limited to samples emitting THz waves
- Imaging method unique to THz waves

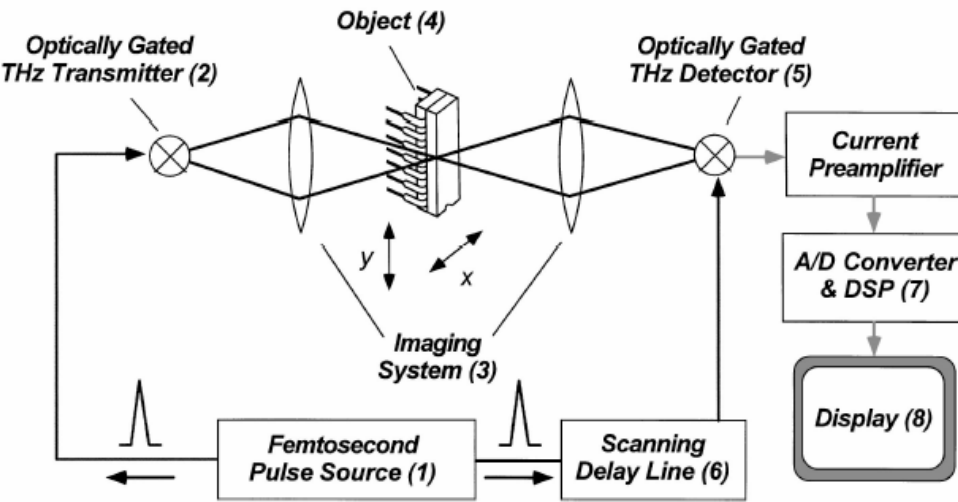
Distribution of surface field in semiconductors
Distribution of supercurrent in superconductors

Pioneering Work of THz Imaging



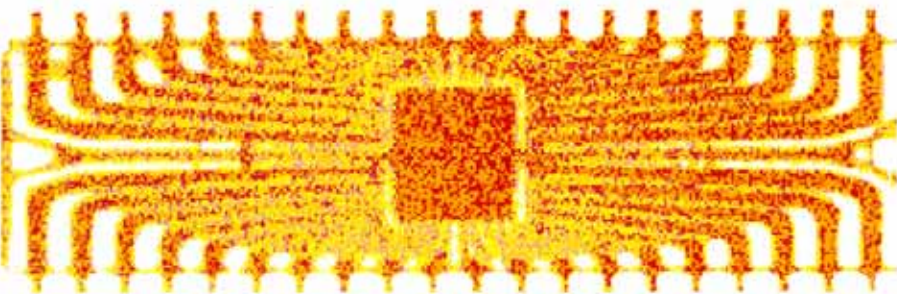
ILE OSAKA

B. B. Hu and D. H. Auston, Opt. Lett. **20** (1995) 1716

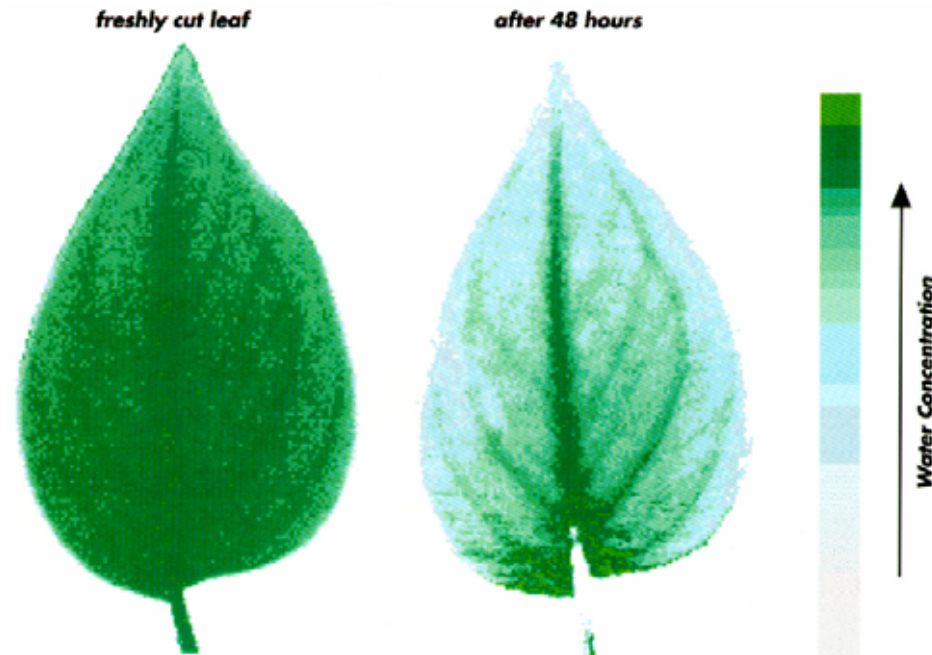


Characteristics of THz waves

absorbed strongly by liquid water
plastic, paper, ceramics transmit THz waves
reflected completely by metals
cannot transmit long distance in air



IC package

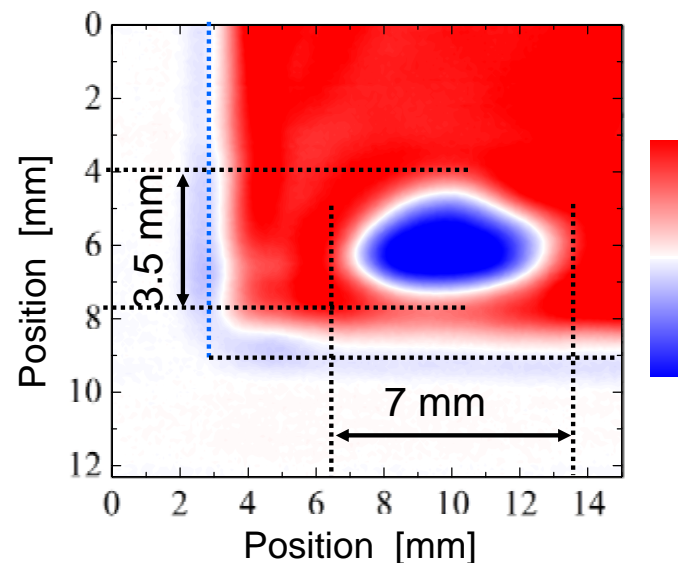
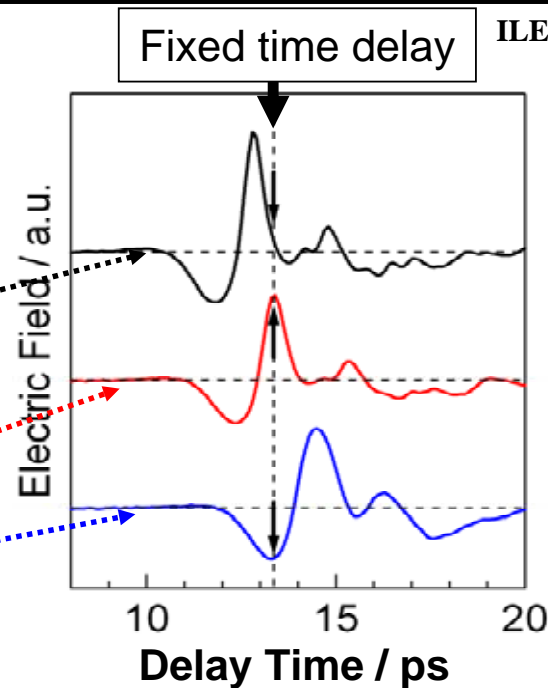
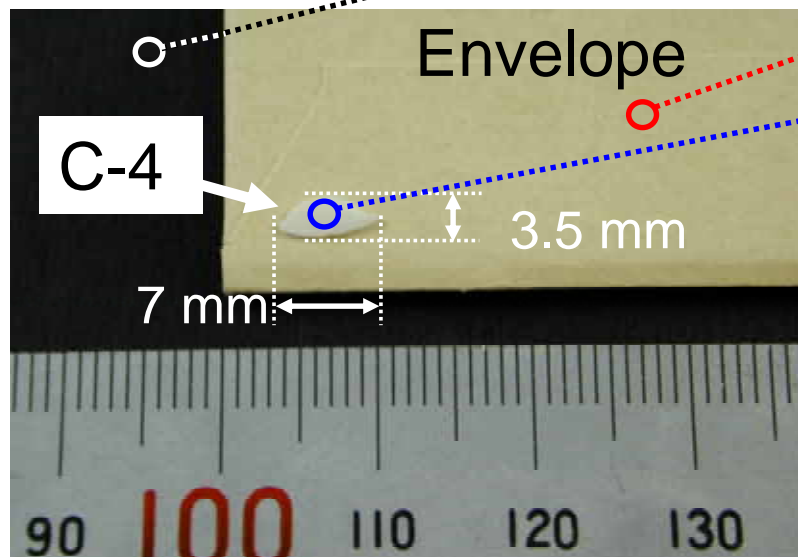


Leaf

Imaging of Plastic Bomb in Mail



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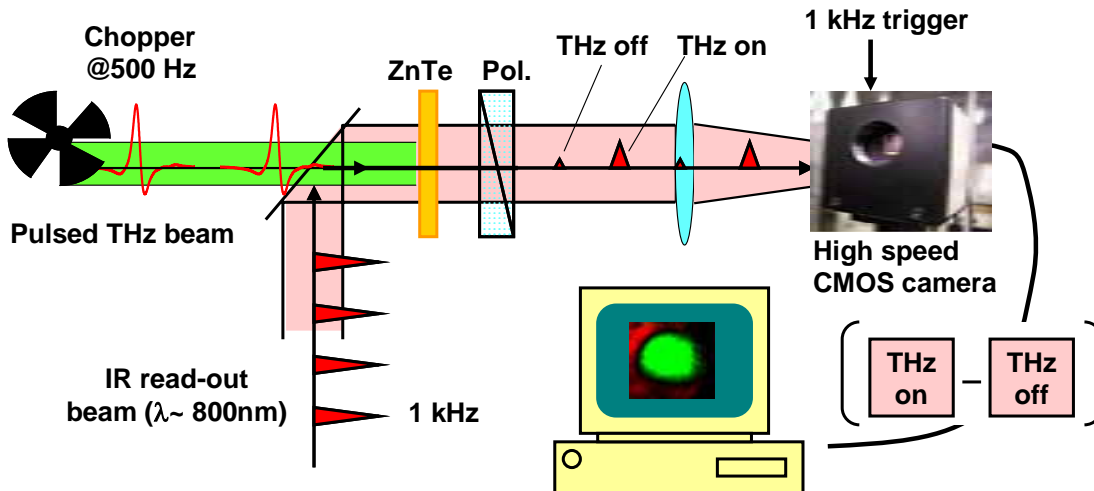
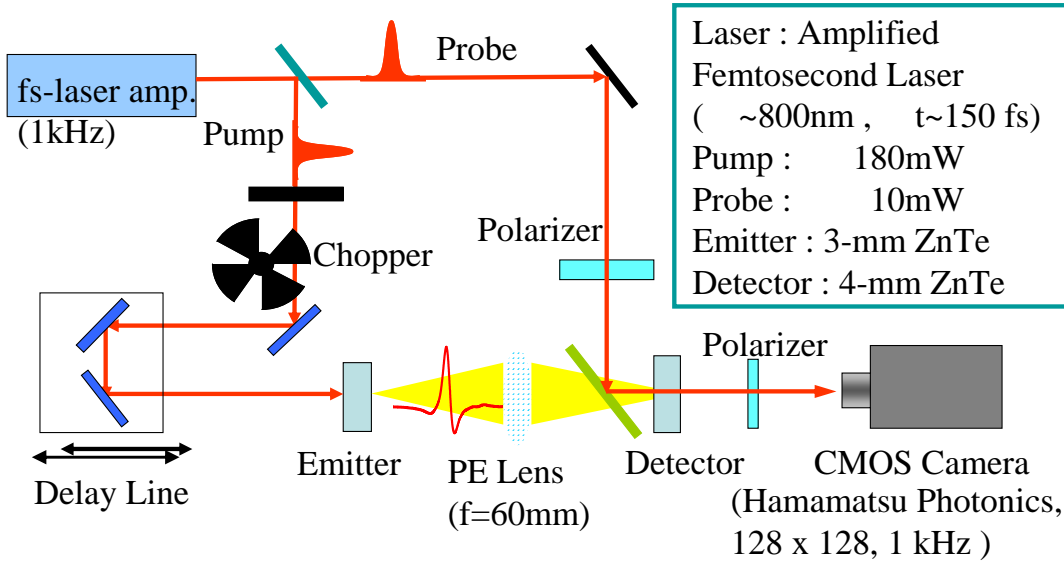


High - speed (Real - time) THz Imaging System



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F. Miyamaru *et al.*, Jpn. J. Appl. Phys. **43** (2004) L489



500 frames/s (2 ms/frame)

Original idea by X. -C. Zhang

Q. Wu, T.D. Hewitt, and X.-C. Zhang ,
 Appl. Phys. Lett. **69** (1996) 1026

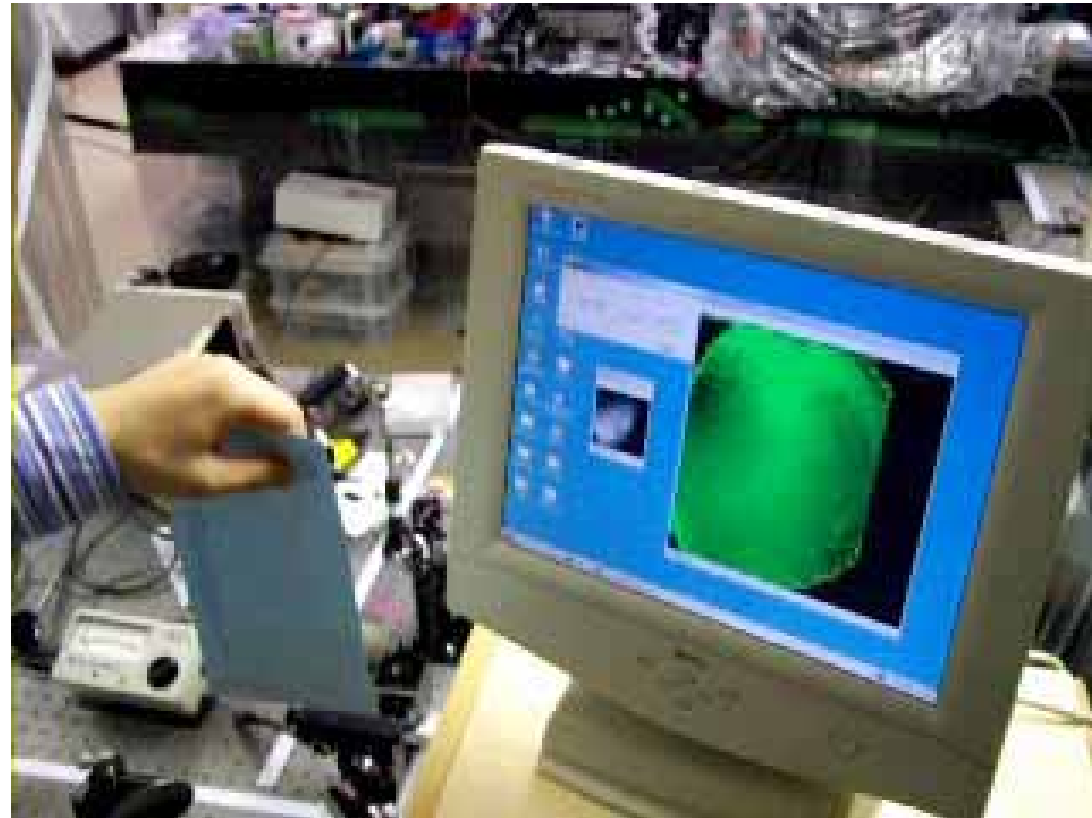
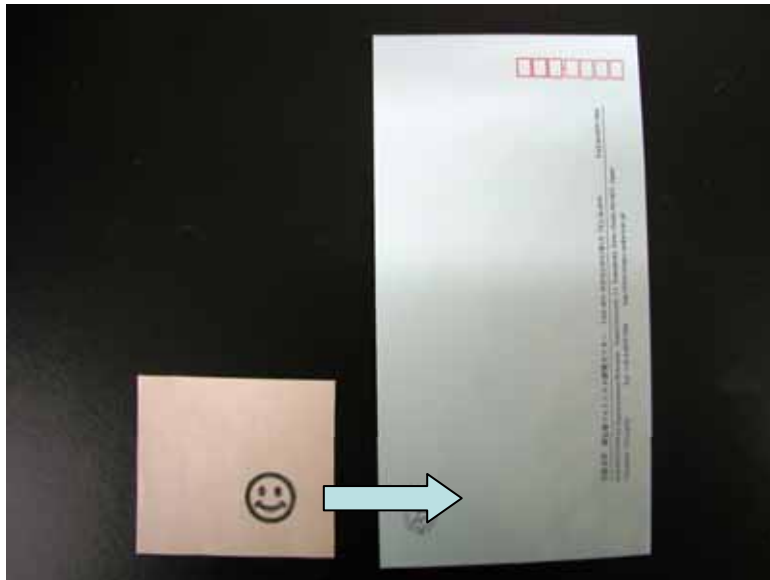


Imaging of Contents in Envelope



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THz wave (T-ray) is safe for human bodies in contrast to X-ray.



Reflection Type Imaging System



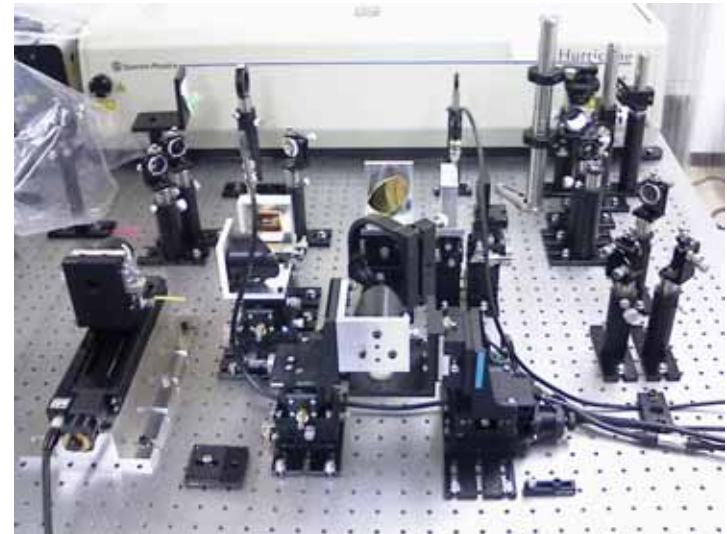
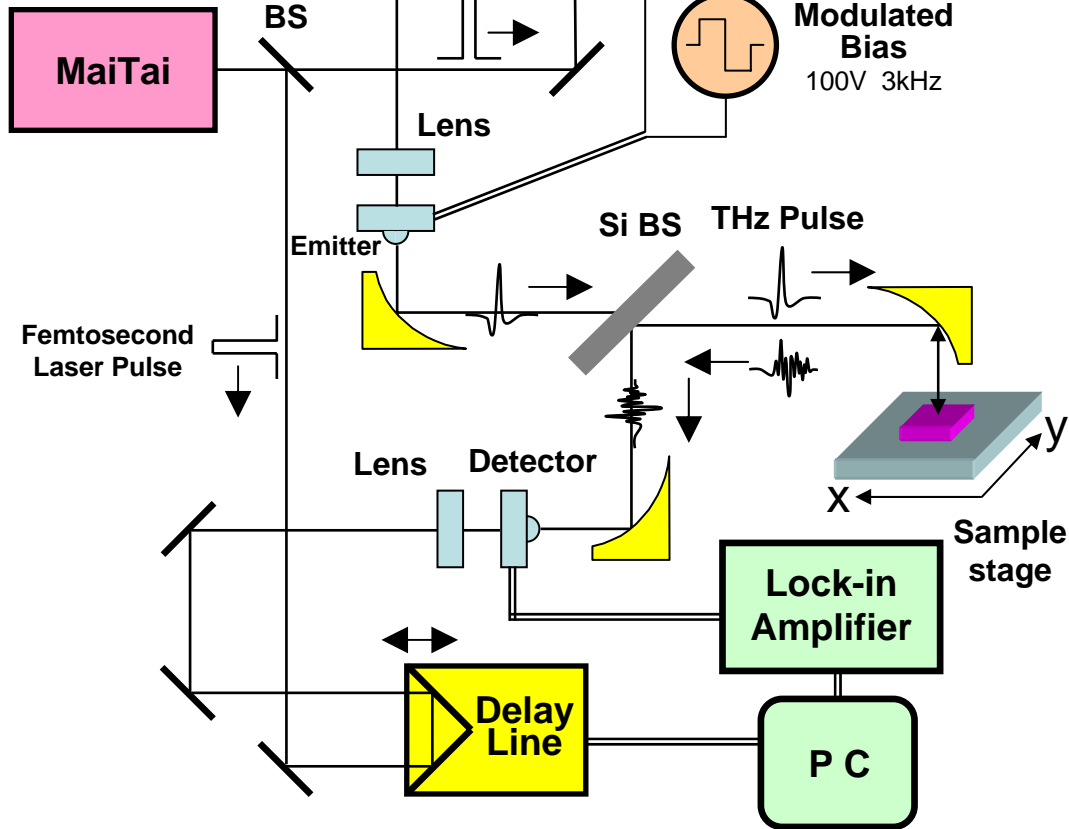
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Raster scan type reflection imaging system

Femtosecond Laser

$\lambda_0=800\text{nm}$, Width=100fs

Repetition Rate 80MHz



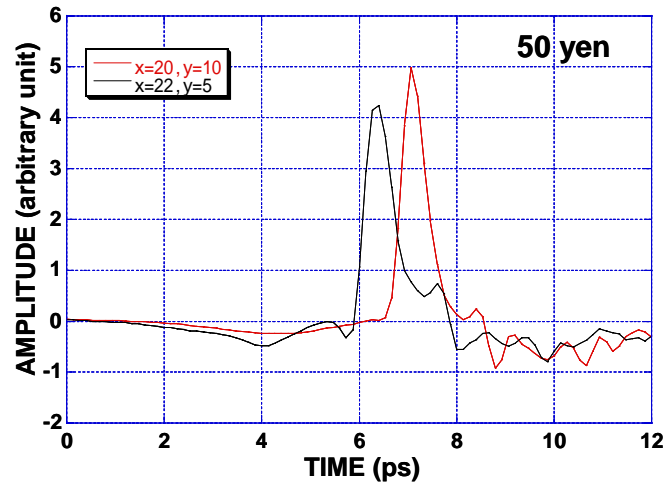
Reflection Image of Coin



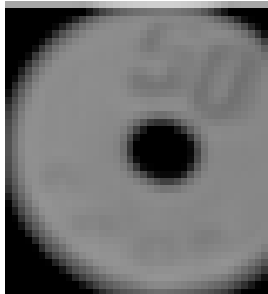
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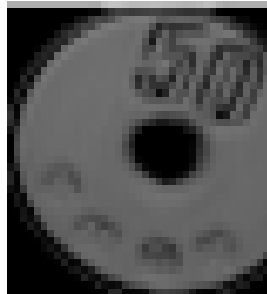
50 yen Japanese coin



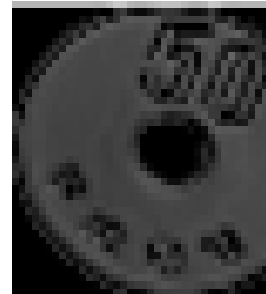
0.23THz



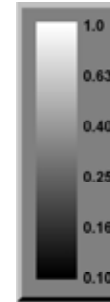
0.46THz



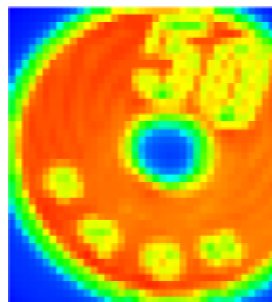
0.69THz



arbitrary unit

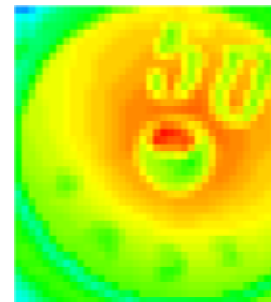


arbitrary unit



Amplitude

ps

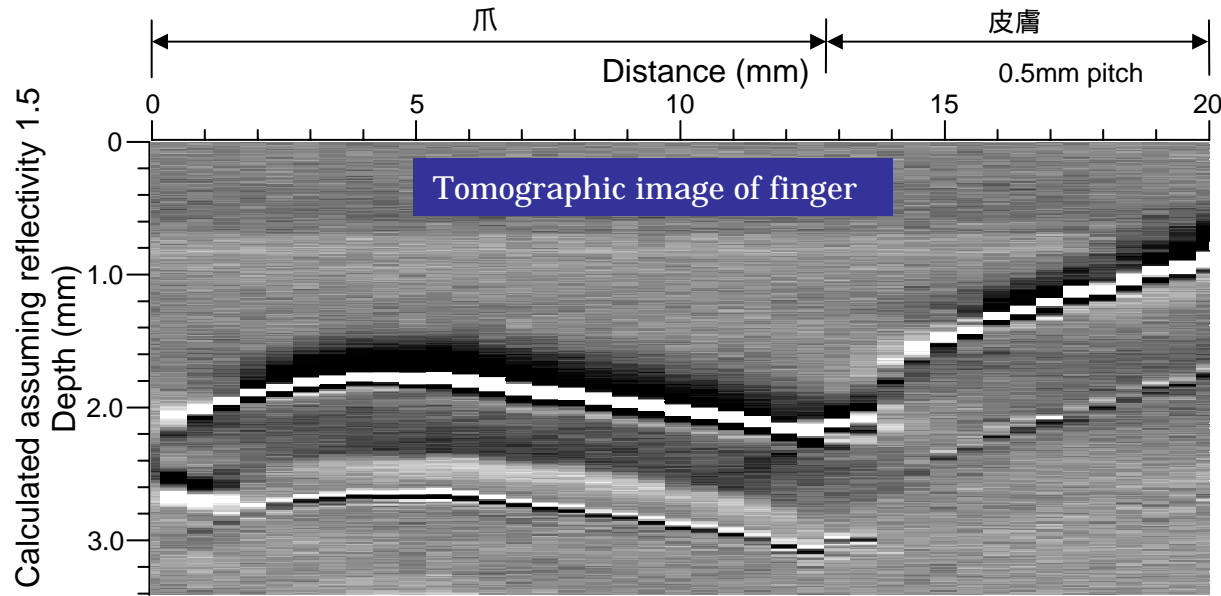


Time delay

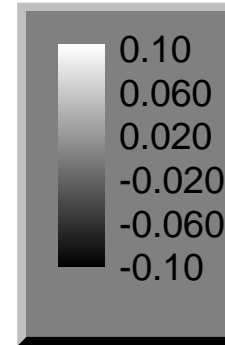
Tomographic Image of Finger



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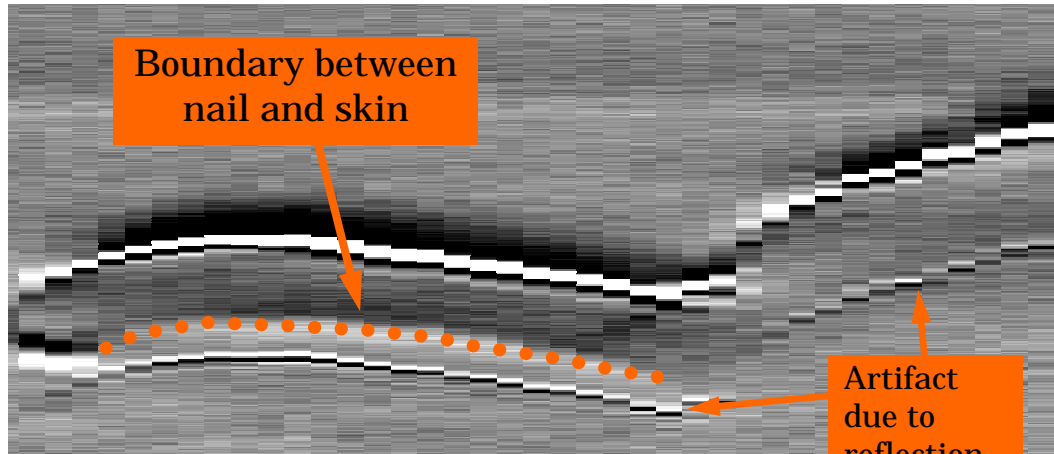
Amplitude (arbitrary unit)



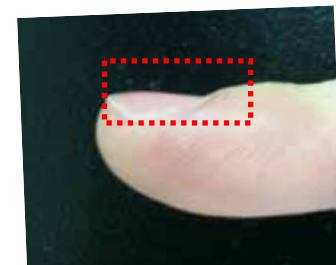
Top view



Broken red line : scanning range



Side view

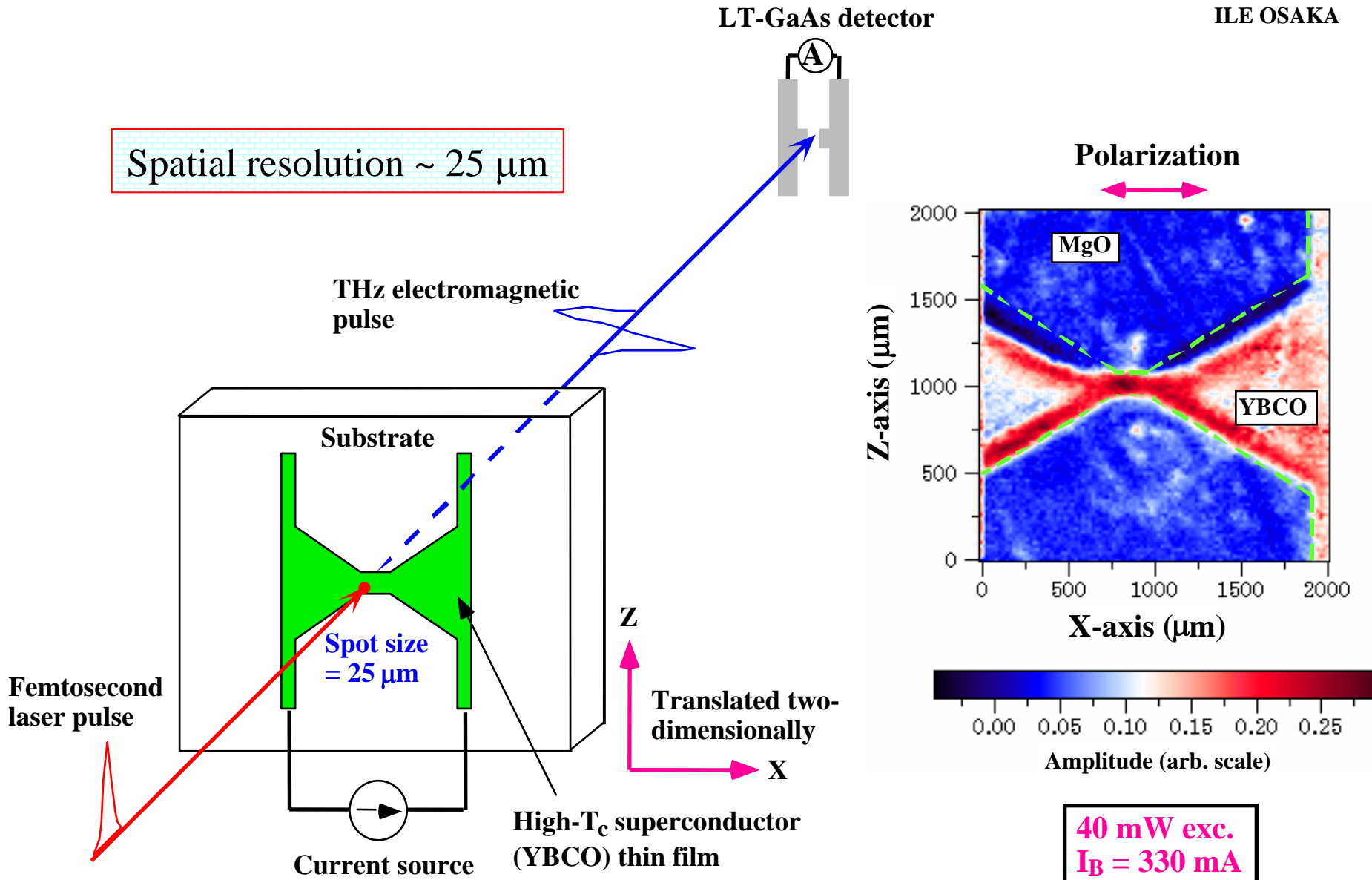


Red square : tomographic imaging region

Supercurrent Distribution by THz Radiation Imaging



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Ultra-short Pulsed Radar Reflectometer

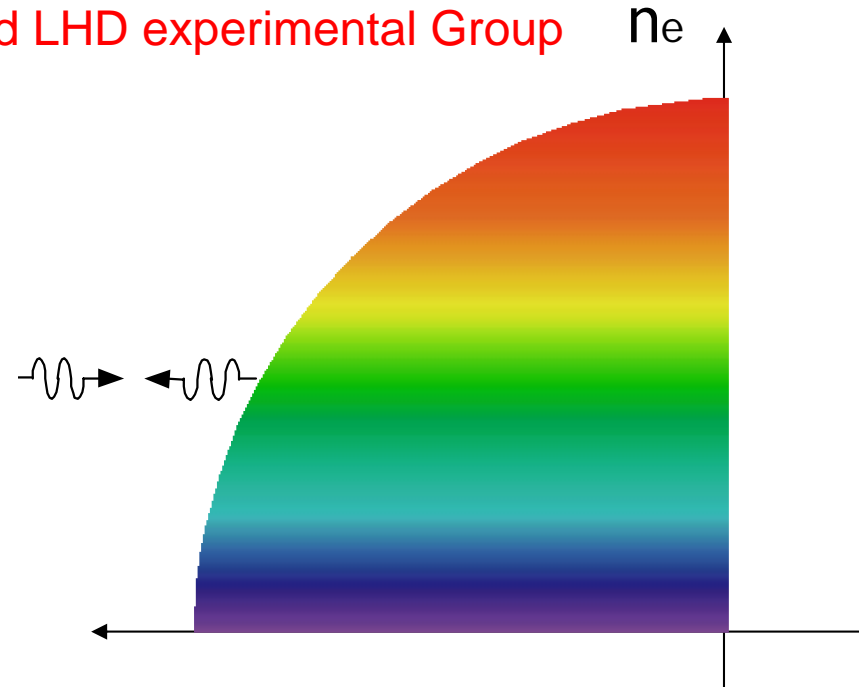
Cutoff frequency

$$f_{pe} = \frac{1}{2\pi} \sqrt{\frac{e^2 n_e}{\epsilon_0 m_e}}$$

Delay time of each frequency component corresponds to the plasma density.

Ka-band Ultra-short Pulsed Radar Reflectometer
10ch (28 ~ 39 GHz)

T.Tokuzawa, K.Kawahata,
and LHD experimental Group



For ITER, very high frequencies are necessary for full coverage
– to ~ 1 THz

THz radiation excited by femtosecond laser is a possible solution.

Problems : low intensity, deflection of reflected beam

Summary

of Imaging and Its Applications

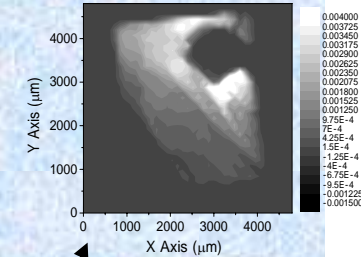
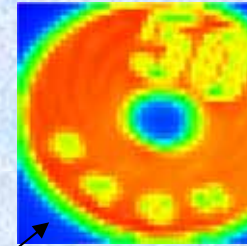
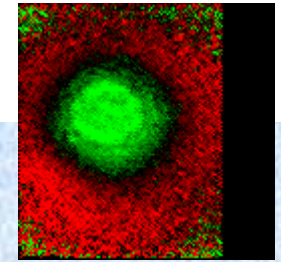
Characteristics of THz Waves

- absorbed strongly by liquid water
- plastic, paper, ceramics transmit THz waves
- reflected completely by metals
- cannot transmit long distance in air

Raster scan type and 2D real time imaging systems are constructed.

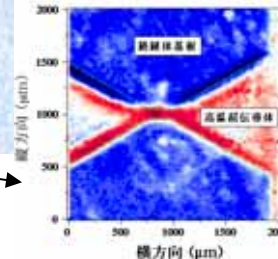
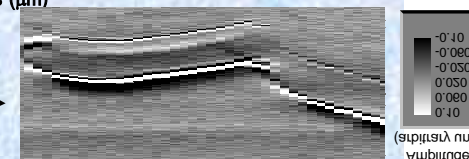
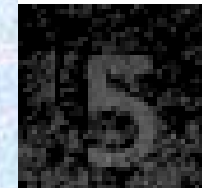
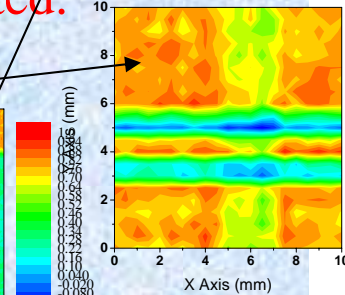
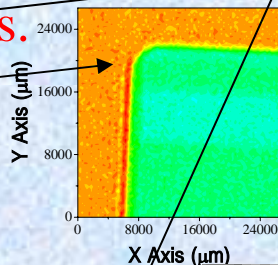
The imaging systems are applied to various samples.

- metal wires
- magnetic cards
- plastic bomb in mail
- coins and watermarks
- finger (tomographic image)
- electric field distribution on semiconductor surfaces
- supercurrent distribution



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Next step is real world applications including plasma diagnostics